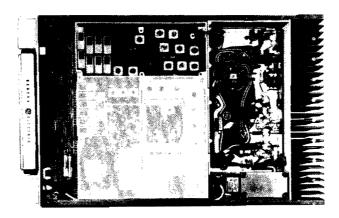


MASTR II MAINTENANCE MANUAL

25-50 MHz, 50-WATT TRANSMITTER



SPECIFICATIONS *

Frequency Range

Power Output

Crystal Multiplication Factor

Frequency Stability

5C-ICOM with EC-ICOM 5C-ICOM or EC-ICOM 2C-ICOMS

Spurious and Harmonic Emission

Modulation

Modulation Sensitivity

Audio Frequency Characteristics

Distortion

Deviation Symmetry

Maximum Frequency Spread: (2 to 8 channels)

25-30 MHz 30-36 MHz 36-42 MHz 42-50 MHz

Duty Cycle

RF Output Impedance

25-50 MHz

50 Watts (Adjustable from 15 to 50 Watts)

3

±0.0005% (-40°C to +70°C) ±0.0002% (0°C to +55°C) ±0.0002% (-40°C to +70°C)

At least 85 dB below full rated power output

Adjustable from 0 to ± 5 kHz swing with instantaneous modulation limiting.

80 to 120 Millivolts

Within +1 dB to -3 dB of a 6-dB/octave preemphasis from 300 to 3000 Hz per EIA standards. Post limiter filter per FCC and EIA.

Less than 2% (1000 Hz) Less than 3% (300 to 3000 Hz)

0.5 kHz maximum

Full 1 dB
Specifications Degradation

.160 MHz .320 MHz
.200 MHz .400 MHz
.240 MHz .270 MHz
.280 MHz .540 MHz

EIA 20% Intermittent

50 Ohms

These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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- WARNING -

Although the highest DC voltage in MASTR II Mobile Equipment is supplied by the vehicle battery, high currents may be drawn under short circuit conditions. These currents can possibly heat metal objects such as tools, rings, watchbands, etc., enough to cause burns. Be careful when working near energized circuits! High-level RF energy in the transmitter Power Amplifier assembly can cause RF burns upon contact. Keep away from these circuits when the transmitter is energized!

DESCRIPTION

MASTR II transmitters are crystal-controlled, phase modulated and designed for one-through eight-frequency operation in the 25 to 50 megahertz band. The solid state transmitter utilizes both integrated circuits (ICs) and discrete components, and consists of the following assemblies:

- Exciter Board; with audio, modulator, amplifier and multiplier stages.
- Power Amplifier Assembly; with amplifier, driver, PA, power control, filter and antenna switch.

CIRCUIT ANALYSIS

EXCITER

The exciter uses nine transistors and two integrated circuits to drive the PA assembly. The exciter can be equipped with up to eight Integrated Circuit Oscillator Modules (ICOMs). The ICOM crystal frequency ranges from approximately 8.33 to 16.67 megahertz, and the crystal frequency is multiplied three times (divided by four

and multiplied by 12 for a multiplication factor of three).

Audio, supply voltages and control functions are connected from the system board to the exciter board through P902.

Centralized metering jack J103 is provided for use with GE Test Set Model 4EX3All or Test Kit 4EX8Kl2. The test set meters the modulator, multiplier and amplifier stages.

ICOMS

Three different types of ICOMs are available for use in the exciter. Each of the ICOMs contains a crystal-controlled Colpitts oscillator, and two of the ICOMs contain compensator ICs. The different ICOMs are:

- 5C-ICOM contains an oscillator and a 5 part-per-million (±0.0005%) compensator IC. Provides compensation for EC-ICOMs.
- EC-ICOM contains an oscillator only. Requires external compensation from a 5C-ICOM.
- 2C-ICOM contains an oscillator and a 2 PPM (±0.0002%) compensator IC.
 Will not provide compensation for an EC-ICOM.

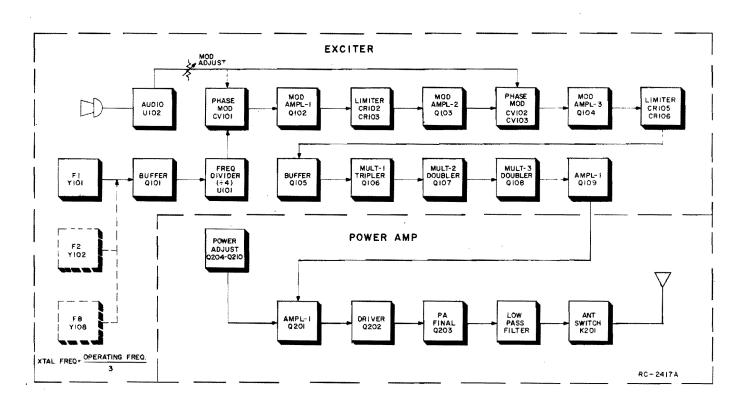


Figure 1 - Transmitter Block Diagram

The ICOMs are enclosed in a dustproof, RF shielded can with the type ICOM (5C-ICOM, EC-ICOM, or 2C-ICOM) printed on the top of the can. Access to the oscillator trimmer is obtained by prying up the plastic tab on the top of the can. The tabs can also be used to pull the ICOMs out of the radio.

Frequency selection is accomplished by switching the ICOM keying lead (terminal 6) to A- by means of the frequency selector switch on the control unit. In single-frequency radios, a jumper from H9 to H10 in the control unit connects terminal 6 of the ICOM to A-. The oscillator is turned on by applying a keyed +10 Volts to the external oscillator load resistor. RF bypassing is provided for all unused keying leads on eight frequency radios. On two frequency radios, the six unused keying leads are shorted to ground.

— CAUTION —

All ICOMs are individually compensated at the factory and cannot be repaired in the field. Any attempt to repair or change an ICOM frequency will void the warranty.

In standard 5 PPM radios using EC-ICOMs, at least one 5C-ICOM must be used. The 5C-ICOM is normally used in the receiver F1 position, but can be used in any transmit or receive position. One 5C-ICOM can provide compensation for up to 15 EC-ICOMs in the transmit and receiver. Should the 5C-ICOM compensator fail in the open mode, the EC-ICOMs will still maintain 2 PPM frequency stability from 0°C to 55°C (+32°F to 131°F) due to the regulated compensation voltage (5 Volts) from the 10-Volt regulator IC. If desired, up to 16 5C-ICOMs may be used in the radio.

The 2C-ICOMs are self-compensated at 2 PPM and will not provide compensation for EC-ICOMs.

Oscillator Circuit

The quartz crystals used in ICOMs exhibit the traditional "S" curve characteristics of output frequency versus operating temperature.

At both the coldest and hottest temperatures, the frequency increases with increasing temperature. In the middle temperature range (approximately 0°C to +55°C), frequency decreases with increasing temperature.

Since the rate of change is nearly linear over the mid-temperature range, the output frequency change can be compensated by choosing a parallel compensation capacitor with a temperature coefficient approximately

equal and opposite that of the crystal.

Figure 2 shows the typical performance of an uncompensated crystal as well as the typical performance of a crystal which has been matched with a properly chosen compensation capacitor.

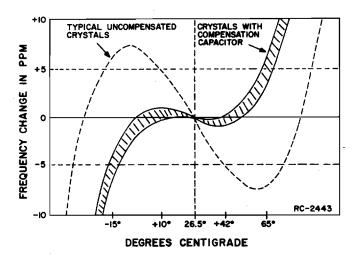


Figure 2 - Typical Crystal Characteristics

At temperatures above and below the mid-range, additional compensation must be introduced. An externally generated compensation voltage is applied to a varactor (voltage-variable capacitor) which is in parallel with the crystal.

A constant bias of 5 Volts (provided from Regulator IC U901 in parallel with the compensator) establishes the varactor capacity at a constant value over the entire mid-temperature range. With no additional compensation, all of the oscillators will provide 2 PPM frequency stability from 0°C to 55°C (32°F to 131°F).

Compensator Circuits

Both the 5C-ICOMs and 2C-ICOMs are temperature compensated at both ends of the temperature range to provide instant frequency compensation. An equivalent ICOM circuit is shown in Figure 3.

The cold end compensation circuit does not operate at temperatures above $0^{\circ}C$. When the temperature drops below $0^{\circ}C$, the circuit is activated. As the temperature decreases, the equivalent resistance decreases and the compensation voltage increases.

The increase in compensation voltage decreases the capacity of the varactor in the oscillator, increasing the output frequency of the ICOM.

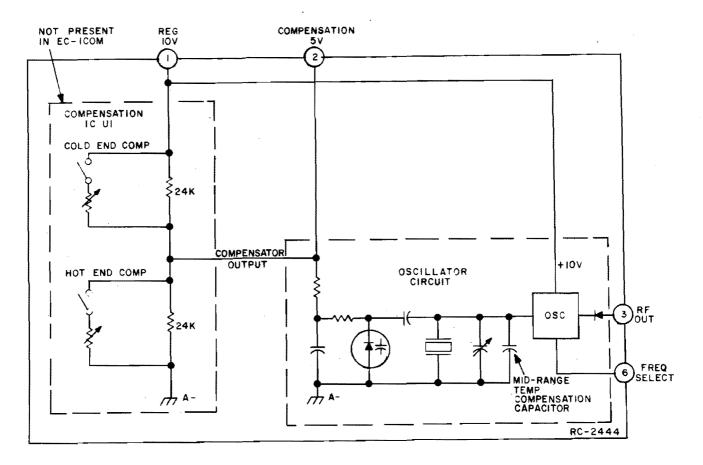


Figure 3 - Equivalent ICOM Circuit

The hot end compensation circuit does not operate at temperatures below +55°C. When the temperature rises above +55°C, the circuit is activated. As the temperature increases, the equivalent resistance decreases and the compensation voltage decreases. The decrease in compensation voltage increases the capacity of the varactor, decreasing the output frequency of the ICOM.

SERVICE NOTE: Proper ICOM operation is dependent on the closely-controlled input voltages from the 10-Volt regulator. Should all of the ICOMs shift off frequency, check the 10-Volt regulator module.

AUDIO IC

The transmitter audio circuitry is contained in audio IC UlO2. A simplified drawing of the audio IC is shown in Figure 4.

Audio from the microphone at pin 12 is coupled through pre-emphasis capacitor C1 to the base of Q1 in the operational amplifier-limiter circuit. Collector voltage for the transistorized microphone preamplifier is supplied from pin 11 through microphone collector load resistor R18 to pin 12.

The operational amplifier-limiter circuit consists of Q1, Q2 and Q3. Q3 provides limiting at high signal levels. The gain of the operational amplifier circuit is fixed by negative feedback through R19, R20 and R126.

The output of Q3 is coupled through a de-emphasis network (R10 and C3) to an active post-limiter filter consisting of C4, C5, C6, R11, R12, R13, R15, R17 and Q4.

Following the post-limiter filter is class A amplifier Q5. The output of Q5 is coupked through MOD ADJUST potentiometer R127 to the phase modulators.

SERVICE NOTE: If the DC voltages to the Audio IC are correct and no audio output can be obtained, replace U102.

For radios equipped with Channel Guard, tone from the encoder is applied to the phase modulators through CHANNEL GUARD MOD ADJUST potentiometer R128, and resistors R110, R121 and R124. Instructions for setting R128 are contained in the modulation adjustment section of the Transmitter Alignment Procedure.

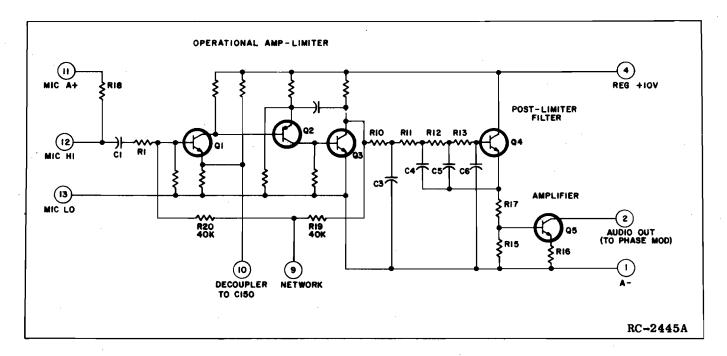


Figure 4 - Simplified Audio IC

FREQUENCY DIVIDER IC

The output at pin 3 of the selected ICOM is coupled through buffer amplifier Q101 to frequency divider U101, which divides the oscillator frequency by 4. The divider consists of two J-K flip-flops connected as a binary counter.

When the transmitter is not keyed (no ICOMs on), Q101 is saturated (turned on) with its collector voltage near zero. Keying the transmitter starts one of the ICOMs, and its output cuts Q101 on and off once each cycle. As Q101 turns off during each cycle, the drop in collector voltage causes the left flip-flop to change state. Assume the flip-flop was in the "0" state (the output at "Q" near A-). The first cycle of the oscillator output causes it to switch to the "1" stage (output at "Q" at approximately 5 Volts). The second cycle will cause the flip-flop to switch back to the "0" state. Therefore, it requires two oscillator cycles to switch the left flipflop through one complete cycle from "0" to "1" and back to "0".

When the left flip-flop switches from "1" to "0", it causes the right flip-flop to change state. It requires two cycles of the left flip-flop to switch the right flip-flop from "0" to "1" and back to "0". Therefore, four cycles of the oscillator output are required for each cycle of output from pin 9 of UlO1.

If U101 was operating into a pure resistive load, its output would be a square wave. However, the modulator circuit presents a tuned load to the IC, so that harmonics are filtered out and the waveform at the junction of C102 and C103 (modulator input) is essentially a sine wave at one-fourth the oscillator frequency. The output of the frequency divider is coupled through DC blocking capacitor C102 to the first modulator stage.

PHASE MODULATORS, AMPLIFIERS AND MULTIPLIERS

The first phase modulator is varactor (voltage-variable capacitor) CV101 in series with tunable coil L101. This network appears as a series-resonant circuit to the RF output of the oscillator. An audio signal applied to the modulator circuit through blocking capacitor C115 varies the bias of CV101, resulting in a phase modulated output. A voltage divider network (R108 and R109) provides the proper bias for varactors CV101, CV102 and CV103.

The output of the first modulator is coupled through blocking capacitor C106 to the base of Class A amplifier Q102. The first modulator stage is metered through a metering network consisting of R115, R150, C107 and CR101. Diodes CR102 and CR103 remove any amplitude modulation in the modulator output.

Following Q102 is another Class A amplifier, Q103. The output of Q103 is applied to the second modulator stage. The second modulator consists of two cascaded modulator circuits consisting of CV102, L102, L103 and CV103. Following the second modulator is a Class A amplifier Q104. The output of the second modulator stage is metered through R133, R145, C117 and CR104, and is applied to the base of buffer Q105. Diodes CR105 and CR106 remove any amplitude modulation in the second modulator output.

Buffer Q105 is saturated when no RF signal is present. Applying an RF signal to Q105 provides a sawtooth waveform at its collector to drive the class C tripler, C106. The tripler stage is metered through R146. The output of Q106 is coupled through tuned circuits T101, T102 and T103 to the base of doubler Q107. T101, T102 and T103 are tuned to one-fourth of the operating frequency. The doubler stage is metered through R147.

The output of Q107 is coupled through tuned circuits T104 and T105 to the base of second doubler Q108. T104 and T105 are tuned to one-half the operating frequency. Q108 is metered through R148.

The output of Q108 is coupled through three tuned circuits (T106, T107 and T108) to the base of amplifier Q109. The circuits are tuned to the transmitter operating frequency.

Q109 is a class C amplifier with a collector feed network consisting of C139, C141, L104, L108 and R143. The stage is metered through R149. The amplifier collector circuit consists of C142, C143, C146 and L105, and matches the amplifier output to the input of the power amplifier assembly.

POWER AMPLIFIER

The PA assembly uses three RF power transistors and seven transistors in the Power Control circuitry to provide a power output of 50 Watts. The broadband PA has no adjustments other than Power Control potentiometer R216.

Supply voltage for the PA is connected through power leads from the system board to feedthrough capacitors C297 and C298 on the bottom of the PA assembly. C297, C298 and C299, L296 and L297 prevent RF from getting on the Power leads. Diode CR295 will cause the main fuse in the fuse assembly to blow if the polarity of the power leads is reversed.

Centralized metering jack J205 is provided for use with GE Test Set Model 4EX3All or Test Kit 4EX8Kl2. The Test Set

meters the Ampl-1 drive (exciter output), Ampl-1 power control, Driver and PA current.

RF AMPLIFIERS

The exciter output is coupled through an RF cable to PA input jack J203. The RF is coupled through DC blocking capacitor C202 to the base of Class C amplifier Q201 through a matching network. The network matches the 50-ohm input to the base of Q201, and consists of C205, C206, C235, L201, L202 and L203.

Part of the RF input is rectified by CR201 and used to activate the Power Control circuit. Another portion of the rectified RF is applied to voltage dividers R223 and R224 for metering the Ampl-1 drive at J205.

Collector voltage to Q201 (Ampl-1) is controlled by the Power Control circuit, and is applied through a collector stabilizing network consisting of L224 and R225 and collector feed network L204 and C207. The collector voltage of Q201 is metered through R235 at J205.

The output of Q201 is applied to the base of Class C driver Q202 through a low-pass filter matching network (C209, C210, L205 and L206). Resistors R202, R203 and R204 lower the gain of Q202. Collector voltage to Q202 is coupled through a collector stabilizing network consisting of L225 and R233 and collector feed network L208 and C213.

Collector current for Q202 is metered across tapped manganin resistor R230 at J205 (Driver Current). The reading is taken on the one-Volt scale with the High Sensitivity button pressed, and read as 10 amperes full scale.

Following Q202 is an interstage coupling network (C214 through C221, L209 through L211, R206 and R207.) The output is applied to the base of the class C PA stage, Q203. Supply voltage is coupled through a collector stabilizing network consisting of L226 and R234 and collector feed network C222 and L212.

Collector current for Q203 is metered across tapped manganin resistor R231 at J205. The reading is taken on the one-Volt scale with the High Sensitivity button pressed, and read as 10 amperes full scale.

The PA output is coupled through an output matching network (C224, C225, C226, L213 and L214,) to an M-derived, constant K low-pass filter. C230 through C233 provides ground isolation for ± ground operation. The filter output is applied to the antenna through antenna switch K201.

- WARNING -

The stud mounted RF Power Transistors used in the transmitter contain Beryllium Oxide, a TOXIC substance. If the ceramic, or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

POWER CONTROL CIRCUIT

When the transmitter is keyed, rectified RF from CR201 is applied to the base of switch Q204, turning it on. Turning on Q204 turns on voltage regulator Q206 which supplies a constant voltage to Power Adjust potentiometer R216.

Q208, Q209 and Q210 operate as an amplifier chain to supply voltage to the collector of Q201 (Ampl-1). The setting of R216 determines the voltage applied to the base of Q208. The higher the voltage at the base of Q208, the harder the amplifiers conduct, supplying more collector voltage to Q201. The lower the voltage at the base of Q208, the less collector voltage is supplied to Q201. Reducing the supply voltage to Q201 reduces the drive to Q202 and Q203, thereby reducing the power output of the PA. The power output can be adjusted by R216 from approximately 15 to 50 Watts.

Temperature protection is provided by Q205, Q207 and thermistor RT201 which is mounted in the PA heatsink. Under normal operating conditions, the circuit is inactive (Q205 is on and Q207 is off). When the heatsink temperature reaches approximately 100°C, the resistance of RT201 decreases. This increases the base voltage applied to Q205, turning it off. Turning off Q205 allows Q207 to turn on, decreasing the voltage at Power Adjust potentiometer R216. This reduces the base voltage to Q208 which causes Q209 and Q210 to conduct less, reducing the collector voltage to Q201 (Ampl-1). This reduces the transmitter output power, keeping the heatsink at a maximum of approximately 100°C. When the heatsink temperature decreases below 100°C, the temperature control circuit turns off, allowing the normal transmitter power output.

CARRIER CONTROL TIMER

The Carrier Control Timer option shuts off the transmitter on each transmission after a one-minute timing cycle, and alerts the operator that the transmitter is off by means of an alarm tone in the speaker. The transmitter can be turned on again by releasing and rekeying the push-to-talk switch on the microphone.

The timing cycle (transmitter keyed time) is normally set at the factory for a duration of one minute. A potentiometer permits the timing cycle to be adjusted from approximately 15 seconds to 3 minutes.

MAINTENANCE

DISASSEMBLY

To service the transmitter from the top:

 Pull the locking handle down, then pry up the top cover at the front notch and lift off the cover.

To service the transmitter from the bottom:

- Pull the locking handle down and pull the radio out of the mounting frame.
- Remove the top cover, then loosen the two bottom cover retaining screws and remove the bottom cover (see Figure 5).
- 3. To gain access to the bottom of the exciter board, remove the six screws

 (A) holding the exciter board and its bottom cover to the module mounting frame, and remove the bottom cover.

To remove the exciter board from the radio:

- 1. Unplug the exciter/PA cable (B)
- Remove the six screws (A) holding the exciter board and its bottom cover to the module mounting frame (see Figure 6).
- Press straight down on the plug-in exciter from the top to avoid bending the pins when unplugging the board from the system board jack.

To remove the PA assembly:

- 1. Remove the PA top cover and unplug the exciter/PA cable (B), the antenna, receiver and PTT cables (C).
- 2. Remove the four side-rail screws (D), and unsolder the power cables from the bottom of the PA assembly if desired.

To remove the PA board:

- 1. Remove the PA top cover and unplug the exciter/PA cable (B) .
- 2. Unsolder the two feedthrough coils $\stackrel{ extbf{(E)}}{ extbf{(E)}}$ and the thermistor leads $\stackrel{ extbf{(F)}}{ extbf{(F)}}$.
- Remove the PA transistor hold-down nuts and spring washers on the bottom of the PA assembly.
- 4. Remove the four PA board mounting screws

 G, the five screws in the filter casting (H), and the retaining screw in Q210 (J), and lift the board out.

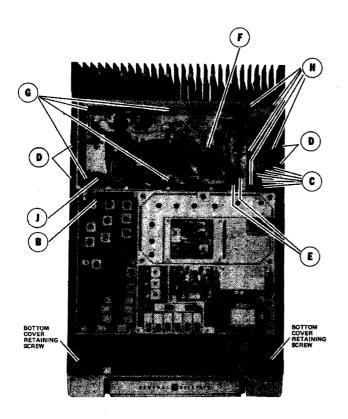


Figure 5 - Disassembly Procedure
Top View

PA TRANSISTOR REPLACEMENT

WARNING -

The stud mounted RF Power Transistors used in the transmitter contin Beryllium Oxide, a TOXIC substance. If the ceramic or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

To replace the PA RF transistors:

- Unsolder one lead at a time with a 50-Watt soldering iron. Use a scribe to hold the lead away from the printed circuit board until the solder cools.
- 2. Turn the transmitter over.
- 3. Hold the body of the transistor to prevent it from turning. Remove the transistor hold-down nut and spring washer through the hole in the heatsink with an 11/32-inch nut-driver for Q201 and Q202, and a 3/8-inch nut-driver for

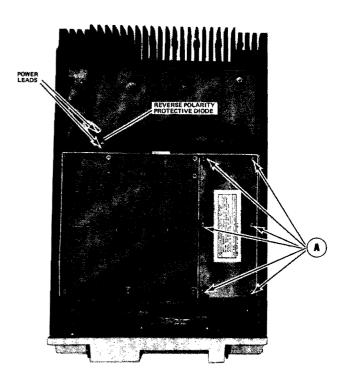
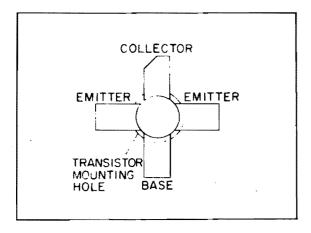


Figure 6 - Disassembly Procedure
Bottom View

Q203. Lift out the transistor, and remove the old solder from the printed circuit board with a de-soldering tool such as a SOLDA PULLT. Special care should be taken to prevent damage to the printed circuit board runs.

- 4. Trim the new transistor leads (if required) to the lead length of the removed transistor. Cut the collector lead at a 45° angle for future identification (see Figure 7). The letter "C" on the top of the transistor indicates the collector.
- 5. Apply a coating of silicon grease around the transistor mounting surface, and place the transistor in the mounting hole. Align the leads as shown in the Outline Diagram. Then hold the body of the transistor and replace the holding-down nut and spring-washer, using moderate torque (6.5 inch-pounds for Q201 and Q202, and 11 inch-pounds for Q203). A torque wrench must be used for this adjustment since transistor damage can result if too little or too much torque is used.

hole.



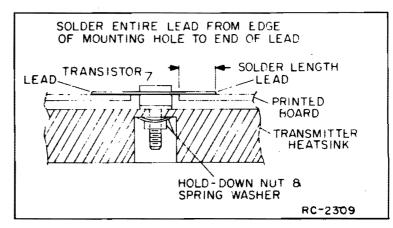


Figure 7 - Lead Identification

6. Make sure that the transistor leads are formed as shown in Figure 8 so that the leads can be soldered to the printed circuit pattern, starting from the inner edge of the mounting

7. Solder the leads to the printed circuit pattern. Start at the inner edge of mounting hole and solder the remaining length of transistor lead to the board. Use care not to use excessive heat that causes the printed

Figure 8 - Lead Forming

wire board runs to lift up from the board. Check for shorts and solder bridges before applying power.

- CAUTION -

Failure to solder the transistor leads as directed may result in the generation of RF loops that could damage the transistor or may cause low power output.

MODULATION LEVEL ADJUSTMENT

The MOD ADJUST (R127) was adjusted to the proper setting before shipment and should not normally require readjustment. This setting permits approximately 75% modulation for the average voice level. The audio peaks which would cause overmodulation are clipped by the modulation limiter. The limiter, in conjunction with the de-emphasis network, instantaneously limits the slope of the audio wave to the modulator, thereby preventing overmodulation while preserving intelligibility.

TEST EQUIPMENT

- 1. An audio oscillator (GE Model 4EX6Al0)
- 2. A frequency modulation monitor
- 3. An output meter or a VTVM
- 4. GE Test Set Models 4EX3All or 4EX8Kl2

PROCEDURE

- 1. Connect the audio oscillator and the meter across audio input terminals J10 (Green-Hi) and J11 (Black-Lo) on GE Test Set, or across P902-6 (Mike High) through a 0.5 microfarad (or larger) DC blocking capacitor, and P902-5 (Mike-Low) on the System Board.
- 2. Adjust the audio oscillator for 1-Volt RMS at 1000 Hz.
- 3. For transmitters without Channel Guard, set MOD ADJUST R127 for a 4.5-kilo-hertz swing with the deviation polarity which gives the highest reading as indicated on the frequency modulation monitor.
- 4. For transmitters with Channel Guard, set Channel Guard MOD ADJUST R128 for zero tone deviation. Next, with the 1-Volt signal at 1000 Hz applied, set MOD ADJUST R127 for a 3.75 kHz deviation. Then remove the signal from the audio oscillator and set Channel Guard MOD ADJUST R128 for 0.75 kHz tone deviation.
- 5. For multi-frequency transmitters, set the deviation as described in Steps 3 or 4 on the channel producing the largest amount of deviation.

PA POWER INPUT

For FCC purposes, the PA power input can be determined by measuring the PA supply voltage and PA current, and using the following formula:

P = PA voltage x PA current

where:

P, is the power input in Watts,

PA voltage is measured with Test Set Model 4EX3All in Position G on the 15-Volt range (read as 15 Volts full scale), and with the polarity switch in the (-) position. With Test Set Model 4EX8Kl2, use the B+ position and the 1-Volt range (read as 15 Volts full scale), with the HIGH SENSITIVITY button pressed and the polarity switch in the (-) position.

PA current is measured with the Test Set in Position G in the Test 1 position, and with the HIGH SENSITIVITY button pressed (10 amperes full scale).

Example:

 $P_i = 12.6 \text{ Volts x } 5.0 \text{ amperes} = 63 \text{ Watts}$

ICOM FREQUENCY ADJUSTMENT

First, check the frequency to determine if any adjustment is required. The frequency should be set with a frequency meter or counter with an absolute accuracy that is 5 to 10 times better than the tolerance to be maintained, and with the entire radio as near as possible to an ambient temperature of 26.5°C (79.8°F).

MASTR II ICOMs should be reset only when the frequency shows deviations in excess of the following limits:

- A. ± 0.5 PPM, when the radio is at 26.5°C (79.8°F).
- B. ± 2 PPM at any other temperature within the range of -5°C to +55°C (+23°F to +131°F).
- C. The specification limit (±2 PPM or ±5 PPM) at any temperature within the ranges of -40°C to -5°C (-40°F to +23°F) or +55°C to +70°C (+131°F to +158°F).

If an adjustment is required, pry up the cover on the top of the ICOM to expose the trimmer, and use one of the following procedures:

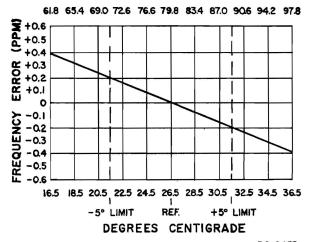
If the radio is at an ambient temperature of 26.5°C (79.8°F), set the oscillator for the correct operating frequency.

- If the radio is not at an ambient temperature of 26.5°C, setting errors can be minimized as follows:
 - A. To hold setting error to ± 0.6 PPM (which is considered reasonable for 5 PPM ICOMS):
 - 1. Maintain the radio at 26.5°C ($\pm5\,^{\circ}\text{C})$ and set the oscillator to desired frequency, or-
 - 2. Maintain the radio at 26.5°C (± 10 °C) and offset the oscillator, as a function of actual temperature, by the amount shown in Figure 9.
- B. To hold setting error to ± 0.35 PPM (which is considered reasonable for 2 PPM ICOMs): Maintain unit at $26.5\,^{\circ}\text{C}$ ($\pm 5\,^{\circ}\text{C}$) and offset the oscillator, as a function of actual temperature, by the amount shown in Figure 9.

For example: Assume the ambient temperature of the radio is 18.5°C (65.4°F). At that temperature, the curve shows a correction factor of 0.3 PPM. (At 25 MHz, 1 PPM is 25 Hz. At 50 MHz, 1 PPM is 50 Hz).

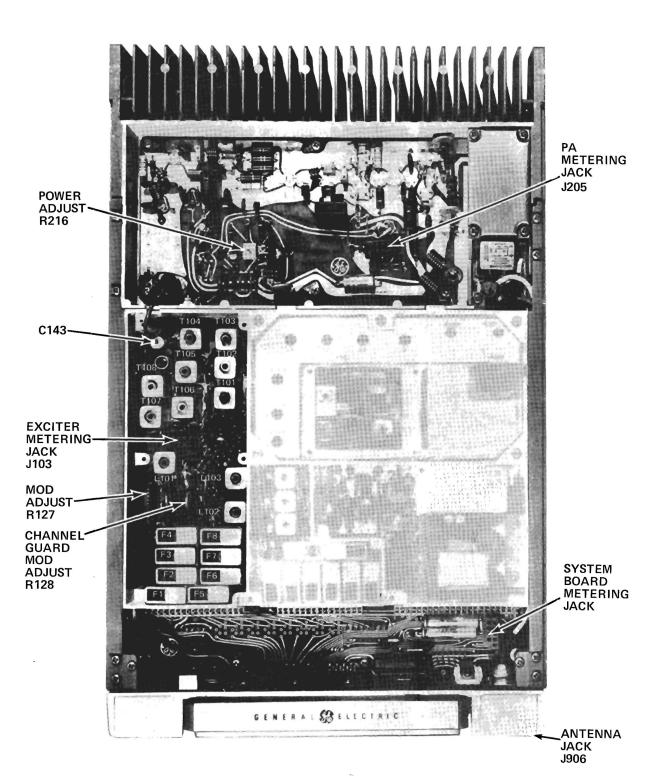
With an operating frequency of 50 MHz, set the oscillator for a reading of 15 Hz (0.3 x 50 Hz) higher than the licensed operating frequency. If a negative correction factor is obtained (at temperatures above 26.5° C), set the oscillator for the indicated PPM lower than the licensed operating frequency.

DEGREES FAHRENHEIT



RC-

Figure 9 - Frequency Characteristics Vs. Temperature



TRANSMITTER ALIGNMENT

LBI-4896

EQUIPMENT REQUIRED

- GE Test Set Model 4EX3All or Test Kit 4EX8K12
- 2. A 50-ohm wattmeter connected to antenna jack J906
- A frequency counter.

PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Place ICOMs on Exciter Board (crystal frequency = operating frequency ; 3).
- For a large change in frequency or a badly mis-aligned transmitter, pre-set the slugs in T101 through T108, and L101, L102 and L103 to the bottom of the coil form.

The tuning frequency for multi-frequency transmitters is determined by the operating frequency and the frequency spread between transmitters. Refer to the table below for maximum frequency spread.

3. For multi-frequency transmitters with a frequency spread less than that specified in column (1), tune the transmitters to the lowest frequency.

For frequency spread exceeding the limits specified in column (1), tune the transmitter using a center frequency tune up ICOM. Except the maximum frequency spread can be extended to the limits specified in column (3) with ldB degradation.

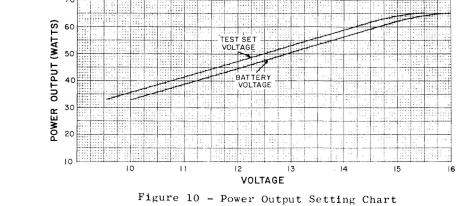
For tuning L101, L102, L103. Always tune L101, L102, L103 on the lowest frequency.

Multi-frequency Transmitter Tuning

Transmitter	MAXIMUM FREQUENCY SPREAD			
Frequency Range	(1) without center tuning	with center tuning	with center tuning (1dB degradation)	
25-30 MHz	.080 MHz	.160 MHz	.320 MHz	
30-36 MHz	.100 MHz	.200 MHz	.400 MHz	
36-42 MHz	.120 MHz	.240 MHz	.470 MHz	
42-50 MHz	.140 MHz	.280 MHz	.540 MHz	

- 4. Connect the red plug on the GE Test Set to the System Board metering jack, and the black plug to the Exciter metering jack. Set the polarity to +, and set the range to the Test 1 position (1-Volt position for 4EXSK12) for all adjustments. NOTE: With the Test Set connected to the PA metering jack, the voltage reading at position "F" with the HIGH SENSITIVITY button pressed may be converted to driver collector current by reading the current as 10 amperes full scale. The voltage reading at position "G" with the HIGH SENSITIVITY button pressed may be converted to PA collector current by reading the current as 10 amperes full scale.
- 5. All adjustments are made with the transmitter keyed. Unkey the transmitter between steps to avoid unnecessary heating.

STEP	METER POSITION	TUNING CONTROL	METER READING	PROCEDURE
1.	A MOD-1	L101	Maximum	Tune L101 for maximum meter reading.
2.	В	L102 & L103	Maximum	Tune L102 and then L103 for the maximum meter reading.
3.	C MULT-1	T101 & T102	See Procedure Tune T101 for a dip in meter reading, and then tune for maximum meter reading.	
4.	D MULT-2	T103, T102, T101 & T104	See Procedure Tune T103 for maximum meter reading and re-adjust T101 for maximum meter reading. Then tune T104 f in meter reading.	
5.	F MULT-3	T105, T104, T106 & T107	See Procedure	Tune T105 for maximum meter reading and re-adjust T104 for maximum meter reading. Then tune T106 for a dip in meter reading and T107 for maximum meter reading.
6.	G AMPL-1	T108, T107 & T106	Maximum	Tune T108 for maximum meter reading, and then re-adjust T107 and T106 for maximum meter reading.
7.	D AMPL-1 DRIVE (on PA)	C143, C156	Maximum	Move the black metering plug to the Power Amplifier metering jack and tune C143 and C156 for maximum meter reading.
8.		R216	,	With the battery voltage at 13.6 Volts or the PA collector voltage at 13.1 Volts, set Power Adjust potentiometer R216 on the PA board for the desired power output (from 15 to 50 Watts). If the battery voltage is not at 13.6 Volts or the collector voltage at 13.1 Volts and full rated output is desired (50 Watts at 13.6 Volts), set R216 for the output power according to the battery voltage or collector voltage shown in Figure 10. NOTE The PA collector voltage is measured as described in the PA POWER INPUT section.



ALIGNMENT PROCEDURE

25-50 MHz, 50-WATT TRANSMITTER

Issue 1

TEST PROCEDURES

These Test Procedures are designed to assist you in servicing a transmitter that is operating—but not properly. Problems encountered could be low power output, tone and voice deviation, defective audio sensitivity, and modulator adjust control set too high. Once a defect is pin-pointed,

refer to the "Service Check" and the additional corrective measures included in the Transmitter Troubleshooting Procedure. Before starting with the Transmitter Test Procedures, be sure the transmitter is tuned and aligned to the proper operating frequency.

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Before bench testing the MASTR II Mobile Radio, be sure of the output voltage characteristics of your bench power supply.

To protect the transmitter power output transistors from possible instant destruction, the following input voltages must not be exceeded:

Transmitter unkeyed: 20 Volts
Transmitter keyed (50 ohm resistive load): 18 Volts
Transmitter keyed (no load or non-resistive load): 15.5 Volts

These voltages are specified at the normal vehicle battery terminals of the radio and take the voltage drop of standard cables into account. The voltage limit shown for a non-optimum load is for "worst case" conditions. For antenna mismatches likely to be encountered in practice, the actual limit will approach the 18 Volt figure.

Routine transmitter tests should be performed at EIA Standard Test Voltages (13.6 VDC for loads of 6 to 16 amperes; 13.4 VDC for loads of 16 to 36 amperes). Input voltages must not exceed the limits shown, even for transient peaks of short duration.

Many commonly used bench power supplies cannot meet these requirements for load regulation and transient voltage suppression. Bench supplies which employ "brute force" regulation and filtering (such as Lapp Model 73) may be usable when operated in parallel with a 12-Volt automotive storage battery.

TEST EQUIPMENT REQUIRED

for test hookup as shown:

1. Wattmeter similar to: 2. VTVM similar to: 3. Audio Generator similar to:

Bird # 43 Jones # 711N

4. Deviation Meter (with a

Measurements # 720

.75 kHz scale) similar to:

Triplett # 850 Heath # IM-21

5. Multimeter similar to:

GE TEST SET MODEL 4EX3A11, MODEL 4EX8K12 or 20,000 ohms-per-Volt voltmeter

GE Model 4EX6Al0

POWER MEASUREMENT

TEST PROCEDURE

- 1. Connect transmitter output from the antenna jack to the wattmeter through a 50-ohm coaxial cable. Make sure the wattmeter is terminated into a 50-ohm load.
- 2. Key the transmitter and check the wattmeter for the desired power output.

SERVICE CHECK

Check the setting of the Power Adjust Control (R216).

Refer to the QUICK CHECKS on the Transmitter Troubleshooting Procedure.

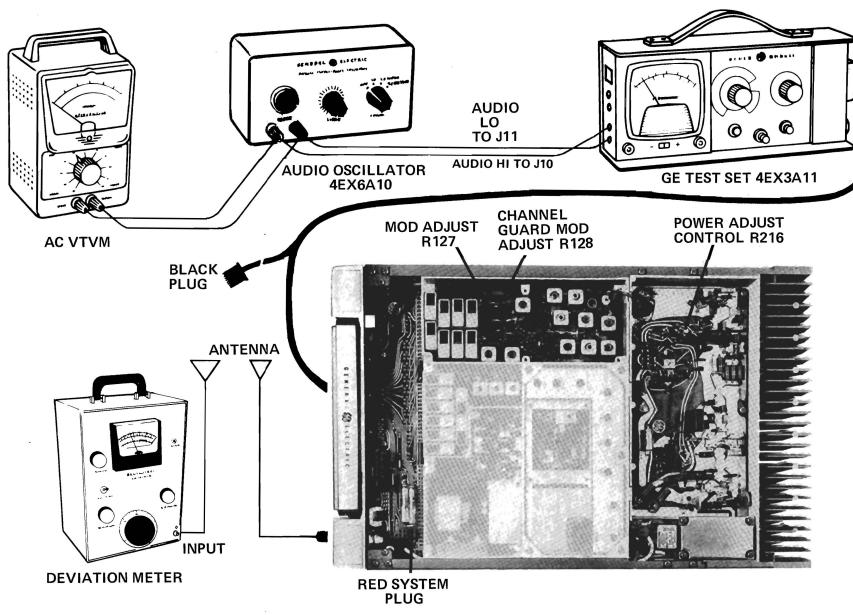
VOICE DEVIATION, SYMMETRY AND AUDIO SENSITIVITY

TEST PROCEDURE

- 1. Connect the test equipment to the transmitter as shown.
- 2. In radios with Channel Guard, set Channel Guard Mod Adjust R128 for zero tone deviation.
- 3. Set the Audio generator output to 1.0 VOLTS RMS and frequency to 1 kHz.
- 4. Key the transmitter and adjust Deviation Meter to carrier frequency.
- 5. Deviation reading should be ± 4.5 kHz in radios without Channel Guard, and ± 3.75 kHz in radios with Channel Guard.
- 6. If necessary, adjust MOD ADJUST control R127 for the proper deviation on plus (+) or minus (-) deviation, whichever is greater.

NOTES: -- MASTR II transmitters are adjusted for 4.5 kHz deviation at the factory. The factory adjustment will prevent the transmitter from deviating more than 5.0 kHz under the worst conditions of frequency, voltage and temperature.

- 7. If the deviation reading plus (+) or minus (-) differs by more than 0.5 kHz, recheck Steps 1 and 2 as shown in the Transmitter Alignment Chart.
- 8. Check Audio Sensitivity by reducing generator output until deviation falls to 3.0 kHz for radios without Channel Guard, or 2.25 kHz for radios with Channel Guard. Voltage should be LESS than 120 millivolts. If not, refer to the Transmitter Troubleshooting Procedure.



TONE DEVIATION WITH CHANNEL GUARD

TEST PROCEDURE

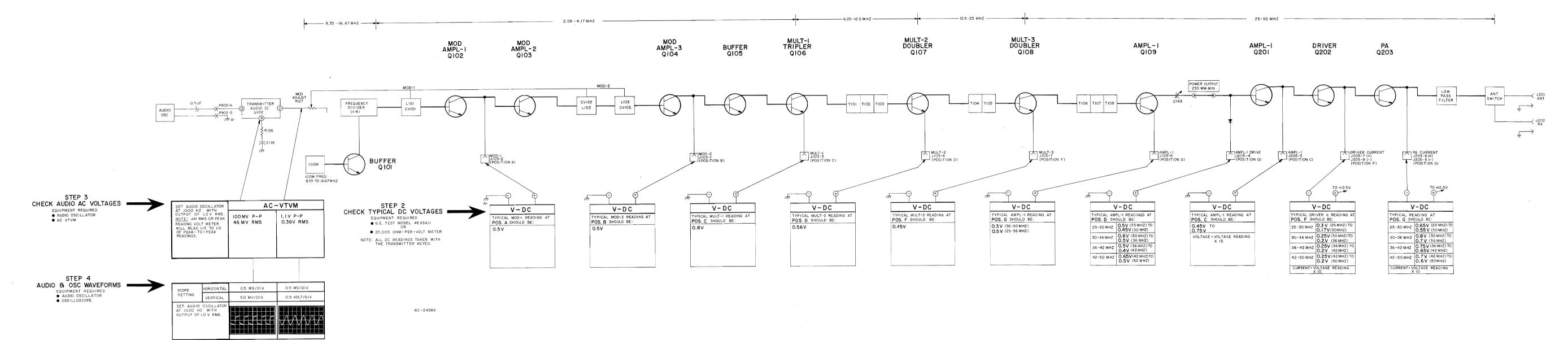
- 1. Set up the Deviation Meter and monitor the output of the transmitter.
- 2. Remove the 1000 Hz signal from the audio generator.
- 3. Key the transmitter and check for 0.75 kHz deviation. If the reading is low or high, adjust Channel Guard MOD ADJUST R128 for a reading of 0.75 kHz.

NOTES:

- 1. On units supplied with Channel Guard, the Phase Modulator Tuning should be adjusted carefully to insure proper performance. (Refer to Steps 1 and 2 in the Transmitter Alignment Chart).
- 2. The Tone Deviation Test Procedures should be repeated every time the Tone Frequency is changed.

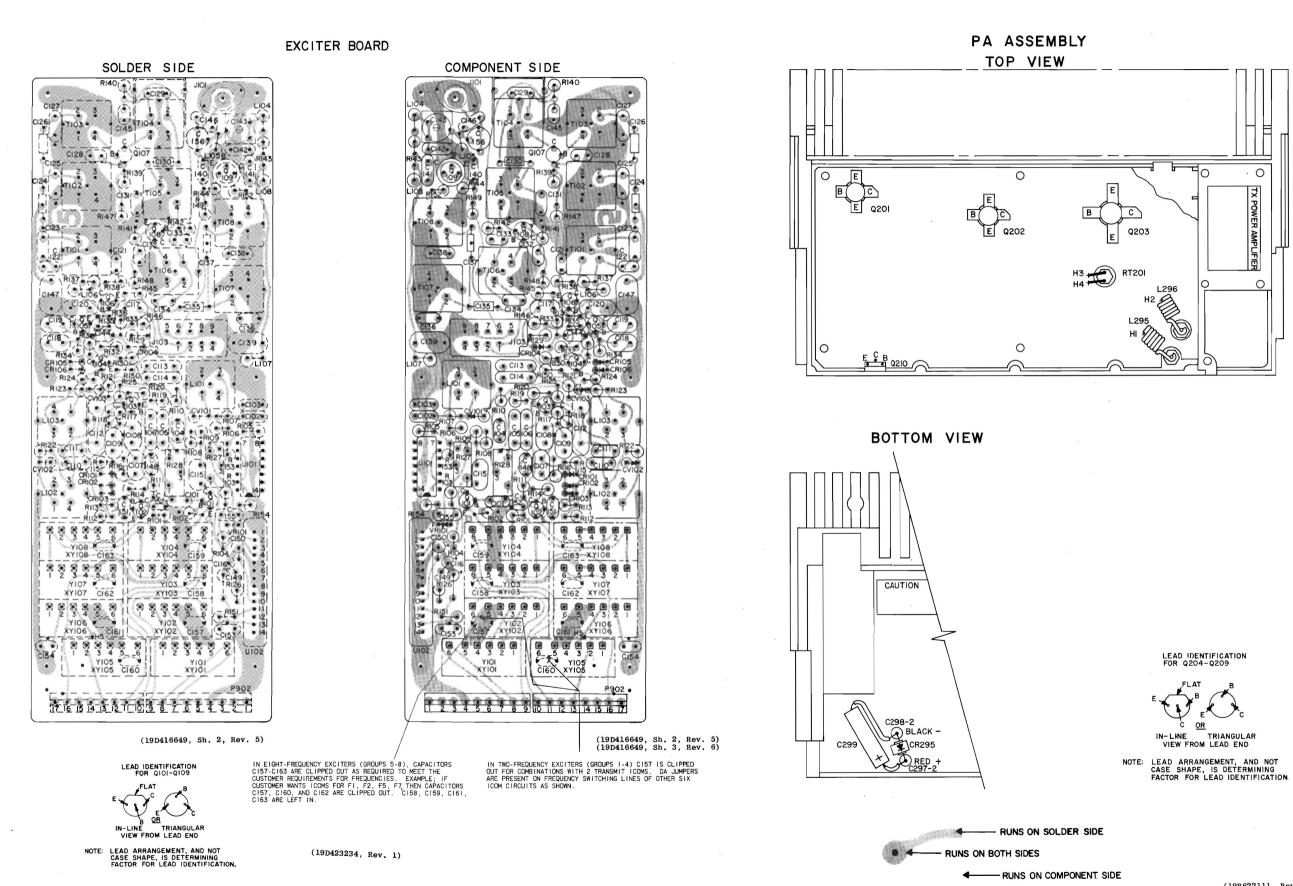
STEP I - QUICK CHECKS

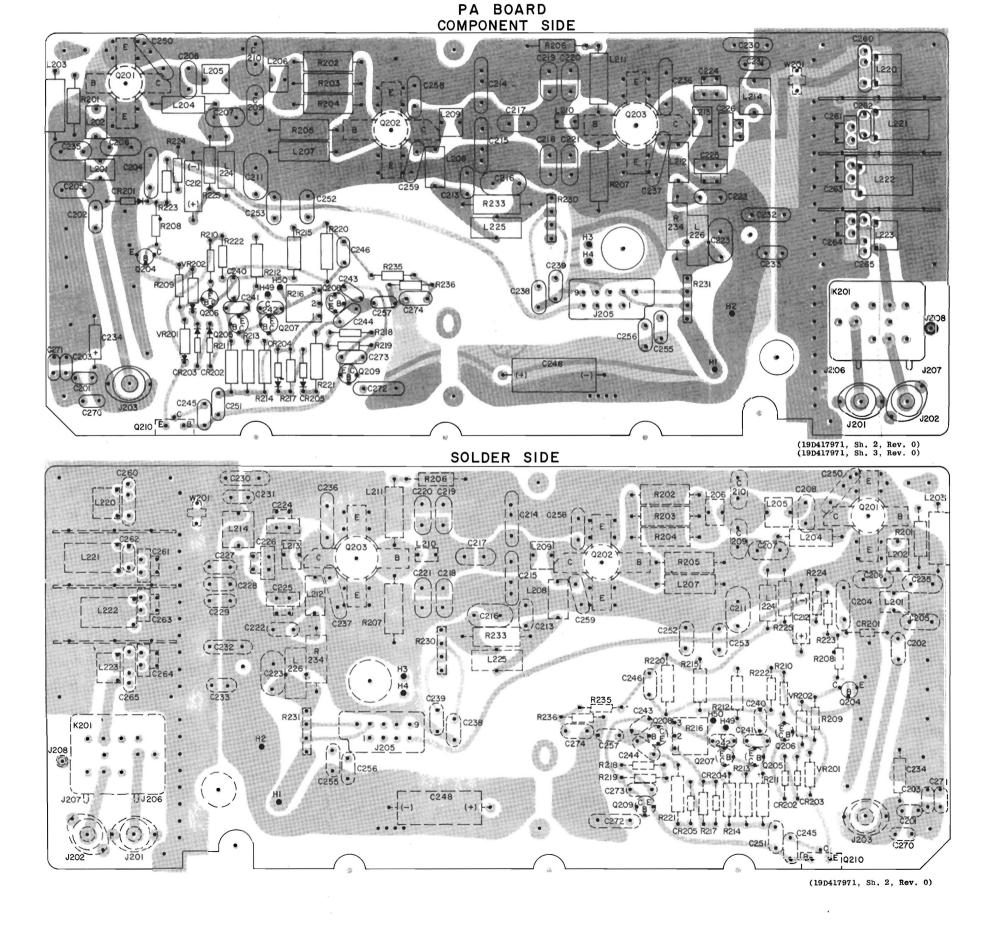
METER		PROBABLE DEFECTIVE STAGE			
POSITION HIGH METE GE TEST SET READING		LOW METER READING	ZERO METER READING		
		EXCITER			
A (MOD-1)	Q102, 10- Volt regulator	Q102, CV101, L101, 10-Volt regulator	ICOM, Q101, U101, L101, Q102, CR101, 10-Volt regulator or Channel Selector switch ground.		
B (MOD-2)	Q104, 10- Volt regulator	Q103, L102, L103, CV102, CV103, Q104	Q103, L102, CV102, L103, CV103, CR104, Q104		
C (MULT-1)	Q105, Q106 T101	Q105, Q106	Q105, Q106, T101		
D (MULT-2)	Q107, T104	T101, T102, T103, Q107	T101, T102, T103, Q107, T104		
F (MULT-3)	Q108, T106	T104, T105, Q108	T104, T105, Q108, T106		
G (AMPL-1)	Q109, C146, R144	T106, T107, T108, Q109, L108	T106, T107, T108, Q109, L104, L107		
	P	OWER AMPLIFIER			
"D" (AMPL-1 DRIVE)		Low Output from Exciter	No output from Exciter, CR201		
"C" (AMPL-1 POWER CONTROL VOLT- AGE)	Q210	Q210	No Exciter output, Q210, Q204, CR201		
"F" (DRIVER CURRENT)	Q202	Q202, Low Output from Q201	Q202, Q201, Check Pos. D & C		
"G" (PA CURRENT)	Q203	Q201, Q202, Q203	Q203, Q202, Q201, Q210		



TROUBLESHOOTING PROCEDURE

25-50 MHz, 50-WATT TRANSMITTER





(19R622111, Rev. 2)

OUTLINE DIAGRAM

25-50 MHz, 50-WATT TRANSMITTER

PARTS LIST	
LBI-4440C	
25-50 MHz EXCITER 19D416659G1-G8	

			·		
		LBI-4440C	C125L	5496219P258	Ceramic disc: 62 pf ±5%, 500 VDCW, temp -80 PPM.
		25-50 MHz EXCITER 19D416659G1-G8	C125M	5496219P257	Ceramic disc: 56 pf ±5%, 500 VDCW, temp -80 PPM.
e.			С125Н	5496219P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp -80 PPM.
	Γ		7 C126LL	5491601P124	Phenolic: 1.8 pf ±5%, 500 VDCW.
SYMBOL	GE PART NO.	DESCRIPTION	C126L	5491601P124	Phenolic: 1.8 pf ±5%, 500 VDCW.
01111002	az i iiii iiio	DEGOMI TION	C126M	5491601P122	Phenolic: 1.2 pf ±5%, 500 VDCW.
			C126H	5491601P122	Phenolic: 1.2 pf ±5%, 500 VDCW.
!		19D416659G1 2 FREQ 25-30 MHz (LL) 19D416659G2 2 FREQ 30-36 MHz (L) 19D416659G3 2 FREQ 36-42 MHz (M)	C127LL	5496219P262	Ceramic disc: 91 pf ±5%, 500 VDCW, temp -80 PPM.
		19D416659G4 2 FREQ 42-50 MHz (LL) 19D416659G6 8 FREQ 25-30 MHz (LL) 19D416659G6 8 FREQ 30-36 MHz (L)	C127L	5496219P258	Ceramic disc: 62 pf ±5%, 500 VDCW, temp -80 PPM.
		190416659G7 8 FREQ 36-42 MHz (M) 190416659G8 8 FREQ 42-50 MHz (H)	C127M	5496219P257	Ceramic disc: 56 pf ±5%, 500 VDCW, temp -80 PPM.
			C127H	5496219P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp -80 PPM.
C101	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C128	19A116080P1	Polyester: 0.01 μf ±20%, 50 VDCW.
C102	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C129LL	5496219P255	Ceramic disc: 47 pf ±5%, 500 VDCW, temp -80 PPM.
C103	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C129L	5496219P251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp -80 PPM.
C104	5494481Pl05	Ceramic disc: 330 pf $\pm 20\%$, 1000 VDCW; sim to RNC Type JF Discap.	C129M	5496219P247	Ceramic disc: 22 pf ±5%, 500 VDCW, temp -80 PPM.
C105 and	19A116655P21	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C1 29H	5496219P244	Ceramic disc: 15 pf £5%, 500 VDCW, temp -80 PPM.
C106	10.11.00.0071.05	D.1	C130LI	5491601P113	Phenolic: 0.47 pf ±5%, 500 VDCW.
C107 thru	19A116080P105	Polyester: 0.047 μf ±10%, 50 VDCW.	C130L	5491601P110	Phenolic: 0.36 pf ±5%, 500 VDCW.
C109 C110	19Al16655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	C130M	5491601P107	Phenolic: 0.27 pf ±5%, 500 VDCW.
and Clll	194110055519	RMC Type JF Discap.	C130H	5491601P105	Phenolic: 0.22 pf ±5%, 500 VDCW.
C112LL	4029003P104	Silver mica: 680 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-20.	C131LI		Ceramic disc: 47 pf ±5%, 500 VDCW, temp -80 PPM.
C112L	4029003P104	Silver mica: 680 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-20.	C131L	5496219P251	Ceramic disc: 33 pf =5%, 500 VDCW, temp -80 PPM.
C112M	5493367P1000K	Mica: 1000 pf ±10%, 100 VDCW; sim to Electro Motive Type DM-20.	C131M	5496219P247	Ceramic disc: 22 pf ±5%, 500 VDCW, temp -80 PPM.
С112Н	5493367P1000K	Mica: 1000 pf ±10%, 100 VDCW; sim to Electro Motive Type DM-20.	C131H	5496219P244	Ceramic disc: 15 pf ±5%, 500 VDCW, temp -80 PPM.
C113 and	19A116655P21	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C132 and C133	19A116080P1	Polyester: 0.01 μf ±20%, 50 VDCW.
C114 C115	19Al16080Pl05	Polyester: 0.047 µf ±10%, 50 VDCW.	С134Ы	5496219P243	Ceramic disc: 13 pf ±5%, 500 VDCW, temp -80 PPM.
C116	5496267P9	Tantalum; 3.3 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	C134L	5496219P240	Ceramic disc: 9.0 pf ±0.25 pf, 500 VDCW, coef -80 PPM.
Cll7 thru	19116080P105	Polyester: 0.047 µf ±10%, 50 VDCW.	C134M	5496219P242	Ceramic disc: 12 pf ±5%, 500 VDCW, temp -80 PPM,
C119 C120	5490008P139	Mica: 330 pf ±10%, 500 VDCW; sim to	С134Н	5496219P238	Ceramic disc: 7.0 pf \pm 0.25 pf, 500 VDCW, coef -80 PPM.
-		Electro Motive Type DM-15.	C135L1	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.
C121 and	19A116080P1	Polyester: 0.01 µf ±20%, 50 VDCW.	C135L	5491601P114	Phenolic: 0.51 pf ±5%, 500 VDCW.
C122 C123LL	5496219P262	Ceramic disc: 91 pf ±5%, 500 VDCW, temp coef	C135M	5491601P115	Phenolic: 0.56 pf ±5%, 500 VDCW.
C123L	5496219P258	-80 PPM. Ceramic disc: 62 pf ±5%, 500 VDCW, temp coef	С135Н	5491601P113	Phenolic: 0.47 pf ±5%, 500 VDCW.
C123M	5496219P257	-80 PPM. Ceramic disc: 56 pf ±5%, 500 VDCW, temp coef	C136LL	İ	Ceramic disc: 13 pf ±5%, 500 VDCW, temp -80 PPM.
С123Н	5496219P254	-80 PPM. Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef	C136L	5496219P240	Ceramic disc: 9.0 pf ±0.25 pf, 500 VDCW, coef -80 PPM.
C124LL	5491601P123	-80 PPM. Phenolic: 1.5 pf ±5%, 500 VDCW.	C136M	5496219P242	Ceramic disc: 12 pf ±5%, 500 VDCW, temp -80 PPM.
C124LL C124L	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.	C136H	5496219P238	Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, coef -80 PPM.
C124M	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.	C137LL	5491601P114	Phenolic: 0.51 pf ±5%, 500 VDCW.
C124H	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.	C137L	5491601P114	Phenolic: 0.51 pf ±5%, 500 VDCW.
C125LL	5496219P262	Ceramic disc: 91 pf ±5%, 500 VDCW, temp coef	C137M	5491601P111	Phenolic: 0.39 pf ±5%, 500 VDCW.
		-80 PPM.	C137H	5491601P111	Phenolic: 0.39 pf ±5%, 500 VDCW.
	•				

SYMBOL | GE PART NO.

DESCRIPTION

	SYMBOL	GE PART NO.	DESCRIPTION
p coef	C138LL	5496219 P 243	Ceramic disc: 13 pf ±5%, 500 VDCW, temp co-
p coef	C138L	5496219P240	-80 PPM. Ceramic disc: 9.0 pf ±0.25 pf, 500 VDCW, to
n accf	01000		coef -80 PPM.
p coef	C138M	5496219P242	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coe -80 PPM.
	С138Н	5496219 P 238	Ceramic disc: 7.0 pf ± 0.25 pf, 500 VDCW, to coef -80 PPM.
	C139	19A116080P107	Polyester: 0.1 µf ±20%, 50 VDCW.
	C140	19Al16655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim RMC Type JF Discap.
coef	C141LL	5490008Pl27	Silver mica: 100 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
coef	C141L	5490008P125	Silver mica: 82 pf ±10%, 500 VDCW; sim to Electro Motive type DM-15.
coef	C141M	5490008P123	Silver mica: 68 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
coef	С141Н	5490008Pl27	Silver mica: 100 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
6	C142LL	5490008P27	Silver mica: 100 pf ±50%, 50 VDCW; sim to Electro Motive Type DM-15.
coef	C142L	5490008P25	Silver mica: 82 pf ±5%, 500 VDCW; sim to Electro Motive type DM-15.
coef	C142M	5490008P25	Silver mica: 82 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
coef	C142H	5490008P24	Silver mica: 75 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
coef	C143	19A116163P5	Variable: approx 5 to 60 pf, 50 VDCW; sim to Amperex 2222-809-08003.
	C144	5494481P105	Ceramic disc: 330 pf ±20%, 1000 VDCW; sim t RMC Type JF Discap.
	C145	19A116080P1	Polyester: 0.01 µf ±20%, 50 VDCW.
coef	C146*	5496219P238	Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, to coef -80 PPM. Added by REV B.
0001	C146LL*	19A116656P12J8	Ceramic: 12 pf, $\pm 5\%$, 0 PPM. Deleted by REV
coef	C146L*	19A116656P12J8	Ceramic: 12 pf, ±5%, 0 PPM. Deleted by RE
coef	C146M*	19A116656P13J8	Ceramic: 13 pf, ±5%, 0 PPM. Deleted by RE
coef	C146H*	19A116656P12J8	Ceramic: 12 pf, ±5%, 0 PPM. Deleted by REV
,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	C147	19A116080P107	Polyester: 0.1 µf ±20%, 50 VDCW.
	C148	5494481P105	Ceramic disc: 330 pf ±20%, 1000 VDCW; sim RMC Type JF Discap.
coef	C149	5496267P10	Tantalum: 22 μf $\pm 20\%$, 15 VDCW; sim to Sprag Type 150D.
temp	C150	5496267P14	Tantalum: 15 μf $\pm 20\%$, 20 VDCW; sim to Sprag Type 150D.
coef	C151	5494481P105	Ceramic disc: 330 pf ±20%, 1000 VDCW; sim t RMC Type JF Discap.
temp	C152 thru -C155	19A116080Pl	Polyester: 0.01 μf ±20%, 50 VDCW.
	C156*	19A116867P1	Variable, ceramic: 2.5-6 pf, +50% -10%, 160 VDCW; sim to 7-S-TRIKO-02. Added by REV B.
	C157* thru C163*	19A116080Pl	Polyester: 0.01 µf ±20%, 50 VDCW. Added by REV C.
			DIODES AND RECTIFIERS
coef	CR101 thru CR106	19A115250P1	Silicon.
temp	CV101 thru CV103	5495769P12	Silicon, capacitive.
coef			JACKS AND RECEPTACLES
temp	J101	19Al16832Pl	Connector, receptacles; sim to Cinch 14H1161
	J103	19B219374Gl	Connector. Includes:
		19A116651P1	Contact; electrical: sim to Malco XO-2864.
	11		1

L101LL 19D416635G9 Coil. L101L 19D416635G1 Coil. L101M 19D416635G1 Coil. L102LL 19D416635G1 Coil. L102LL 19D416635G1 Coil. L102LL 19D416635G1 Coil. L102LL 19D416635G1 Coil. L102LM 19D416635G1 Coil. L102LM 19D416635G1 Coil. L103LM 19D416635G1 Coil. L104LM 7488078P9 Choke, RF: 2.70 ub ±10%, 1.20 ohms DC res max; sint to Jeffers 4411-12. L104LM 7488078P7 Choke, RF: 1.50 ub ±10%, 0.50 ohms DC res max; sint to Jeffers 4411-12. L104LM 7488078P7 Choke, RF: 1.50 ub ±10%, 0.50 ohms DC res max; sint to Jeffers 4411-13. L105LL 7488078P7 Choke, RF: 1.60 ub ±10%, 0.50 ohms DC res max; sint to Jeffers 4411-13. L105LL 7488078P3 Choke, RF: 0.68 ub ±10%, 0.15 ohms DC res max; sint to Jeffers 4411-13. L105LM 7488078P1 Choke, RF: 0.68 ub ±10%, 0.09 ohms DC res max; sint to Jeffers 4411-13. L105M 7488078P1 Choke, RF: 0.33 ub ±10%, 0.09 ohms DC res max; sint to Jeffers 4411-3. L106M 7488078P16 Choke, RF: 0.31 ub ±10%, 0.09 ohms DC res max; sint to Jeffers 4411-3. L108M 7488078P16 Choke, RF: 0.0 ub ±10%, 0.09 ohms DC res max; sint to Jeffers 4421-7. L108M 7488078P16 Choke, RF: 0.0 ub ±10%, 0.09 ohms DC res max; sint to Jeffers 4421-7. L108M 7488078P16 Silicon, NPN. L108M 7488078P17 Silicon, NPN. L109M 19A115330P1 Silicon, NPN. L109M 19A115330P1 Silicon, NPN. Earlier than REV A: L101A13330P1 Silicon, NPN. Earlier than REV A: L103LM 3R77961K Composition: 560 ohms ±10%, 1/2 w. C000000000000000000000000000000000000	SYM	DESCRIPTION	GE PART NO.	SYMBOL
LIOILL 19D41663509 Coil. LIOIM 19D41663501 Coil. LIOIM 19D41663501 Coil. LIO2M 19D41663501 Coil. LIO3M 19D41663501 Coil. LIO4M 7488079P Choke, RF: 2.70 µh f10%, 1.20 chms DC res max; sim to Joffers 4411-12. LIO4M 7488079P Choke, RF: 1.50 µh f10%, 0.50 chms DC res max; sim to Joffers 4411-10. LIO5M 7488079P Choke, RF: 1.50 µh f10%, 0.30 chms DC res max; sim to Joffers 4411-10. LIO5M 7488079P5 Choke, RF: 0.47 µh f10%, 0.30 chms DC res max; sim to Joffers 4411-1. LIO5M 7488079P4 Choke, RF: 0.37 µh f10%, 0.00 chms DC res max; sim to Joffers 4411-1. LIO5M 7488079P3 Choke, RF: 0.37 µh f10%, 0.00 chms DC res max; sim to Joffers 4421-7. LIO5M 7488079P3 Choke, RF: 0.37 µh f10%, 0.00 chms DC res max; sim to Joffers 4422-11. LIO5M 7488079P3 Choke, RF: 3.9 µh f10%, 0.00 chms DC res max; sim to Joffers 4422-11. LIO6M 7488079P3 Choke, RF: 3.9 µh f10%, 0.00 chms DC res max; sim to Joffers 4422-11. LIO6M 7488079P3 Choke, RF: 3.9 µh f10%, 0.00 chms DC res max; sim to Joffers 4422-11. LIO6M 7488079P3 Silicon, NPN. Silicon, NPN. Silicon, NPN. Silicon, NPN. Earlier than REV C and earlier: 19A115330P1 Silicon, NPN. Earlier than REV A: 19A115330P1 Silicon, NPN. Earlier than REV A: 19A115328P1 Silicon, NPN. Earlier than REV C and earlier:	R10	TRANSPONEDS		
L101L 19D416635G17 C011. L101H 19D416635G18 C011. L102L 19D416635G18 C011. L102L 19D416635G18 C011. L102L 19D416635G17 C011. L102M 19D416635G18 C011. L103L 19D416635G18 C011. L103M 19D416635G18 C011. L103M 19D416635G18 C011. L103M 19D416635G18 C011. L104M 7488079P9 C001. L104L 7488079P9 C004, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13. L104L 7488079P7 C004, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104M 7488079P7 C004, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 C004, RF: 1.50 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P5 C004, RF: 0.68 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-10. L105M 7488079P4 C004, RF: 0.68 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4411-10. L105M 7488079P3 C004, RF: 0.68 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4411-10. L105M 7488079P3 C004, RF: 0.77 µh ±10%, 0.09 ohms DC res max; sim to Jeffers 4411-10. L105M 7488079P3 C004, RF: 0.33 µh ±10%, 0.09 ohms DC res max; sim to Jeffers 4411-10. L105M 7488079P30 C004, RF: 0.33 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4421-7. L108 7488079P30 C004, RF: 0.30 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4421-7. L108 198219594P2 C004 RF: 0.90 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11.	R10		19D416635G9	1.10111.
L101M 19D416635G1 Coil. L102L 19D416635G8 Coil. L102L 19D416635G8 Coil. L102L 19D416635G8 Coil. L102M 19D416635G8 Coil. L103L 19D416635G8 Coil. L103L 19D416635G8 Coil. L103L 19D416635G8 Coil. L103M 19D416635G1 Coil. L104L 7488079P8 Choke, RF: 2.70 mh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-12. L104M 7488079P7 Choke, RF: 2.20 mh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-12. L104M 7488079P7 Choke, RF: 1.50 mh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P7 Choke, RF: 1.50 mh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 1.50 mh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8. L105L 7488079P3 Choke, RF: 0.48 mh ±10%, 0.15 ohms DC res max; sim to Jeffers 4411-8. L105M 7488079P3 Choke, RF: 0.47 mh ±10%, 0.09 ohms DC res max; sim to Jeffers 4411-8. L105H 7488079P3 Choke, RF: 0.47 mh ±10%, 0.09 ohms DC res max; sim to Jeffers 4411-3. L105H 7488079P3 Choke, RF: 0.0 mh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L106 7488079P3 Choke, RF: 0.9 mh ±10%, 0.00 ohms DC res max; sim to Jeffers 4421-7. L108 7488079P3 Choke, RF: 39.0 mh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. L108 7488079P3 Choke, RF: 39.0 mh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. L108 7488079P3 Choke, RF: 39.0 mh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. L108 7488079P3 Choke, RF: 39.0 mh ±10%, 2.00 ohms DC res max; sim to Jeffers 4422-11. L109 19B219594P2 Contact strip: 8 pins. L100 19B219594P3 Contact strip: 9 pins. L100 19B219594P3 Silicon, NPN. L100 19B219594P3 Silicon, NPN. L100 19B215330P1 Silicon, NPN. L101 19B215330P1 Silicon, NPN. L109 19B215328P1 Silic	R10			
L101H 19D416635G18 Coil. L102LL 19D416635G8 Coil. L102R 19D416635G7 Coil. L102R 19D416635G1 Coil. L102R 19D416635G1 Coil. L102R 19D416635G1 Coil. L103LL 19D416635G1 Coil. L103L 19D416635G1 Coil. L103L 19D416635G1 Coil. L103M 19D416635G1 Coil. L103M 19D416635G1 Coil. L103M 19D416635G1 Coil. L104H 7488078P9 Choke, RF: 2.70 µb ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13. L104M 7488078P8 Choke, RF: 1.50 µb ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104M 7488078P7 Choke, RF: 1.50 µb ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104M 7488078P7 Choke, RF: 1.50 µb ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105LL 7488078P6 Choke, RF: 0.68 µb ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8. L105M 7488078P3 Choke, RF: 0.68 µb ±10%, 0.15 ohms DC res max; sim to Jeffers 4411-4. L105M 7488078P3 Choke, RF: 0.68 µb ±10%, 0.15 ohms DC res max; sim to Jeffers 4411-3. L105M 7488078P3 Choke, RF: 0.68 µb ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-4. L105M 7488078P3 Choke, RF: 0.70 µb ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L105M 7488078P3 Choke, RF: 1.00 µb ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L105M 7488078P3 Choke, RF: 39.0 µb ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L106M 7488078P3 Choke, RF: 39.0 µb ±10%, 0.00 ohms DC res max; sim to Jeffers 442-11. L107M 7488078P3 Silicon, NPN. L108M 7488078P3 Silicon, NPN. L109M 19A115330P1 Silicon, NPN. L109M 19A115330P1 Silicon, NPN. L109M 19A115330P1 Silicon, NPN. L109M 19A115330P1 Silicon, NPN. Earlier than REV A: L109M 19A115330P1 Silicon, NPN. Earlier than REV A: L109M 19A115330P1 Silicon, NPN. Earlier than REV A: L109M 19A115330P1 Silicon, NPN. L109M 19A115328P1 Sili	R10			
L102LL 19D41663569 Coil. L102L 19D416635617 Coil. L102W 19D416635618 Coil. L103L 19D416635618 Coil. L103L 19D416635618 Coil. L103L 19D41663561 Coil. L103L 19D41663561 Coil. L103M 19D41663561 Coil. L103H 19D41663561 Coil. L103H 19D41663561 Coil. L104L 7488079P8 Choke, RF: 2.70 µh 110%, 1.20 ohms DC res max; sim to Jeffers 4411-13. L104L 7488079P7 Choke, RF: 2.20 µh 110%, 1.00 ohms DC res max; sim to Jeffers 4411-10. L104M 7488079P7 Choke, RF: 1.50 µh 110%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104H 7488079P7 Choke, RF: 1.50 µh 110%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 1.50 µh 110%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 1.00 µh 110%, 0.30 ohms DC res max; sim to Jeffers 4411-1. L105H 7488079P3 Choke, RF: 0.30 µh 110%, 0.15 ohms DC res max; sim to Jeffers 4411-3. L105H 7488079P3 Choke, RF: 0.33 µh 110%, 0.07 ohms DC res max; sim to Jeffers 4411-3. L105H 7488079P6 Choke, RF: 0.30 µh 110%, 0.07 ohms DC res max; sim to Jeffers 4411-7. L106 7488079P6 Choke, RF: 30.0 µh 110%, 0.60 ohms DC res max; sim to Jeffers 4421-7. L107 Choke, RF: 30.0 µh 110%, 2.00 ohms DC res max; sim to Jeffers 4422-7. L108 7488079P50 Choke, RF: 39.0 µh 110%, 2.00 ohms DC res max; sim to Jeffers 4422-11. L108 19B219594P2 Contact strip: 8 pins. L108 19B219594P3 Contact strip: 8 pins. L108 19B219594P3 Silicon, NPN. L108 19B115330P1 Silicon, NPN. L108 19B115330P1 Silicon, NPN. L109 19B115328P1 Silicon, NPN. L109 1BB115328P1 Silicon, NPN. L109 1BB11532	R11			į.
L102L 19D416635G17 Coil. L102M 19D416635G1 Coil. L103L 19D416635G18 Coil. L103L 19D416635G17 Coil. L103L 19D416635G17 Coil. L103M 19D416635G17 Coil. L103M 19D416635G18 Coil. L103H 19D416635G18 Coil. L104L 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13. L104L 7488079P8 Choke, RF: 2.20 µh ±10%, 1.00 ohms DC res max; sim to Jeffers 4411-10. L104M 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104M 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105LL 7488079P6 Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-10. L105LL 7488079P5 Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-5. L105M 7488079P4 Choke, RF: 0.83 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4411-4. L105H 7488079P3 Choke, RF: 0.33 µh ±10%, 0.07 ohms DC res max; sim to Jeffers 4411-4. L105H 7488079P16 Choke, RF: 0.30 µh ±10%, 0.07 ohms DC res max; sim to Jeffers 4411-3. L106B 7488079P10 Choke, RF: 0.30 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L108 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L109 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L109 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L109 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L109 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L109 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L109 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L109 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L109 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-3. L100 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-10. L100 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-10. L100 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-10. L100 Choke, RF: 0.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-10.	R11			
L102M 19D41663561 Coil. L103L 19D41663561 Coil. L103L 19D41663561 Coil. L103M 19D41663561 Coil. L104L 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13. L104M 7488079P8 Choke, RF: 2.20 µh ±10%, 1.00 ohms DC res max; sim to Jeffers 4411-12. L104M 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104M 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P5 Choke, RF: 0.47 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-5. L105M 7488079P4 Choke, RF: 0.47 µh ±10%, 0.09 ohms DC res max; sim to Jeffers 4411-3. L105M 7488079P3 Choke, RF: 0.30 µh ±10%, 0.07 ohms DC res max; sim to Jeffers 4411-3. L106M 7488079P16 Choke, RF: 0.30 µh ±10%, 0.07 ohms DC res max; sim to Jeffers 4411-3. L106M 7488079P10 Choke, RF: 39.0 µh ±10%, 0.60 ohms DC res max; sim to Jeffers 4411-7. L108 7488079P50 Choke, RF: 39.0 µh ±10%, 2.00 ohms DC res max; sim to Jeffers 4421-7. L108 7488079P50 Choke, RF: 39.0 µh ±10%, 2.00 ohms DC res max; sim to Jeffers 4421-7. L108 19B115330P1 Silicon, NPN. L108 19B115330P1 Silicon, NPN. L109 19A115330P1 Silicon, NPN. L109 19A11532P2 Silicon, NPN. L109 19A11532P2 Silicon, NPN. L109 19A11532P2 Silicon, NPN. L109 19A11532P2 Silicon, NPN. L109 19A11532	R11			l
L102H 19D416635G8 Coil. L103L 19D416635G8 Coil. L103H 19D416635G1 Coil. L103M 19D416635G1 Coil. L103M 19D416635G1 Coil. L104H 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13. L104L 7488079P8 Choke, RF: 2.20 µh ±10%, 1.00 ohms DC res max; sim to Jeffers 4411-12. L104M 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104H 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P5 Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8. L105M 7488079P5 Choke, RF: 0.60 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4411-3. L105M 7488079P4 Choke, RF: 0.33 µh ±10%, 0.09 ohms DC res max; sim to Jeffers 4411-3. L105M 7488079P3 Choke, RF: 0.33 µh ±10%, 0.07 ohms DC res max; sim to Jeffers 4411-3. L106 7488079P16 Choke, RF: 10.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4421-7. L108 7488079P50 Choke, RF: 39.0 µh ±10%, 0.60 ohms DC res max; sim to Jeffers 4422-7. L108 19B219594P2 Contact strip: 8 pins. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 1.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-10. Choke, RF: 1.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-10. Choke, RF: 1	R11			I
L103LL 19D41663569 Coil. L103L 19D416635G17 Coil. L103R 19D416635G18 Coil. L103R 19D416635G18 Coil. L104L 7488079P9 Choke, RF: 2.70 µb ±10%, 1.20 ohms DC res max; sin to Jeffers 4411-13. L104L 7488079P8 Choke, RF: 2.20 µb ±10%, 1.00 ohms DC res max; sin to Jeffers 4411-12. L104M 7488079P7 Choke, RF: 1.50 µb ±10%, 0.50 ohms DC res max; sin to Jeffers 4411-10. L104H 7488079P7 Choke, RF: 1.50 µb ±10%, 0.50 ohms DC res max; sin to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 1.50 µb ±10%, 0.30 ohms DC res max; sin to Jeffers 4411-10. L105L 7488079P5 Choke, RF: 1.00 µb ±10%, 0.30 ohms DC res max; sin to Jeffers 4411-8. L105M 7488079P5 Choke, RF: 0.47 µb ±10%, 0.15 ohms DC res max; sin to Jeffers 4411-8. L105M 7488079P3 Choke, RF: 0.47 µb ±10%, 0.09 ohms DC res max; sin to Jeffers 4411-4. L105B 7488079P3 Choke, RF: 0.47 µb ±10%, 0.09 ohms DC res max; sin to Jeffers 4411-3. L106B 7488079P16 Choke, RF: 0.10 µb ±10%, 0.60 ohms DC res max; sin to Jeffers 4421-7. L108 7488079P30 Choke, RF: 39.0 µb ±10%, 0.60 ohms DC res max; sin to Jeffers 4422-7. L108 7488079P30 Choke, RF: 39.0 µb ±10%, 2.00 ohms DC res max; sin to Jeffers 4422-7. L108 7488079P30 Silicon, NPN. L108 19A115330P1 Silicon, NPN. L109 19A115330P1 Silicon, NPN. L109 19A115330P1 Silicon, NPN. L109 19A115330P1 Silicon, NPN. L109 19A115328P1 Silicon, NPN. L200 19A115328P1 Silicon, NPN. L201 19A115328P1 Silicon, NPN. L202 3R152P682J Composition: 6800 ohms ±5%, 1/4 w. L203 3R152P682J Composition: 6800 ohms ±5%, 1/4 w. L204 1REV C and earlier:	R11			
L103L 19D416635G17 Coil. L103M 19D416635G1 Coil. L103H 19D416635G1 Coil. L104L 7488079P9 Choke, RF: 2.70 µh 110%, 1.20 chms DC res max; sim to Jeffers 4411-13. L104L 7488079P8 Choke, RF: 2.20 µh 110%, 0.50 chms DC res max; sim to Jeffers 4411-12. L104M 7488079P7 Choke, RF: 1.50 µh 110%, 0.50 chms DC res max; sim to Jeffers 4411-12. L104M 7488079P7 Choke, RF: 1.50 µh 110%, 0.50 chms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 1.00 µh 110%, 0.50 chms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 0.68 µh 110%, 0.30 chms DC res max; sim to Jeffers 4411-5. L105M 7488079P6 Choke, RF: 0.68 µh 110%, 0.09 chms DC res max; sim to Jeffers 4411-5. L105M 7488079P3 Choke, RF: 0.47 µh 110%, 0.09 chms DC res max; sim to Jeffers 4411-3. L105M 7488079P3 Choke, RF: 0.0 µh 110%, 0.60 chms DC res max; sim to Jeffers 4411-3. L105M 7488079P3 Choke, RF: 10.0 µh 110%, 0.60 chms DC res max; sim to Jeffers 4421-7. L108 7488079P30 Choke, RF: 39.0 µh 110%, 2.00 chms DC res max; sim to Jeffers 4422-71. L108 Table Part of P	R11			
L103M 19D416635G1 Coil. L103H 19D416635G18 Coil. L104LL 7488079P9 Choke, RF: 2.70 µh f10%, 1.20 ohms DC res max; sim to Jeffers 4411-13. L104L 7488079P8 Choke, RF: 2.20 µh f10%, 1.00 ohms DC res max; sim to Jeffers 4411-12. L104M 7488079P7 Choke, RF: 1.50 µh f10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104H 7488079P7 Choke, RF: 1.50 µh f10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105LL 7488079P6 Choke, RF: 1.00 µh f10%, 0.30 ohms DC res max; sim to Jeffers 4411-10. L105L 7488079P5 Choke, RF: 1.00 µh f10%, 0.30 ohms DC res max; sim to Jeffers 4411-10. L105M 7488079P4 Choke, RF: 0.47 µh f10%, 0.09 ohms DC res max; sim to Jeffers 4411-3. L105H 7488079P3 Choke, RF: 0.33 µh f10%, 0.09 ohms DC res max; sim to Jeffers 4411-3. L106 7488079P16 Choke, RF: 1.0.0 µh f10%, 0.09 ohms DC res max; sim to Jeffers 4411-3. L107 T488079P3 Choke, RF: 1.0.0 µh f10%, 0.00 ohms DC res max; sim to Jeffers 4421-7. L108 7488079P3 Choke, RF: 10.0 µh f10%, 0.60 ohms DC res max; sim to Jeffers 4422-71. L109 T488079P3 Choke, RF: 10.0 µh f10%, 0.60 ohms DC res max; sim to Jeffers 4422-71. L109 T488079P3 Choke, RF: 10.0 µh f10%, 0.60 ohms DC res max; sim to Jeffers 4422-71. L109 T488079P3 Silicon, NPN. L108 Silicon, NPN. L109	R11			- 1
L103H 19D416635G18 Coil. L104LL 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13. L104L 7488079P8 Choke, RF: 2.20 µh ±10%, 1.00 ohms DC res max; sim to Jeffers 4411-10. L104M 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L104H 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-10. L105LL 7488079P6 Choke, RF: 1.00 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4411-5. L105L 7488079P6 Choke, RF: 1.00 µh ±10%, 0.00 ohms DC res max; sim to Jeffers 4411-5. L105M 7488079P4 Choke, RF: 0.47 µh ±10%, 0.09 ohms DC res max; sim to Jeffers 4411-3. L105H 7488079P3 Choke, RF: 0.33 µh ±10%, 0.07 ohms DC res max; sim to Jeffers 4411-3. L106	R11			
L104LL 7488079P9	R11			l
Sim to Jeffers 4411-13.	R11			
L104M 7488079P7 Choke, RF: 1.50 µh ±10%, 0.50 chms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 1.50 µh ±10%, 0.50 chms DC res max; sim to Jeffers 4411-10. L105L 7488079P6 Choke, RF: 1.00 µh ±10%, 0.30 chms DC res max; sim to Jeffers 4411-8. L105L 7488079P5 Choke, RF: 0.68 µh ±10%, 0.15 chms DC res max; sim to Jeffers 4411-5. L105M 7488079P4 Choke, RF: 0.47 µh ±10%, 0.09 chms DC res max; sim to Jeffers 4411-4. L105H 7488079P3 Choke, RF: 0.33 µh ±10%, 0.07 chms DC res max; sim to Jeffers 4411-3. L106 7488079P16 Choke, RF: 0.33 µh ±10%, 0.07 chms DC res max; sim to Jeffers 4411-3. L107 Choke, RF: 10.0 µh ±10%, 0.60 chms DC res max; sim to Jeffers 4412-3. L108 7488079P50 Choke, RF: 39.0 µh ±10%, 2.00 chms DC res max; sim to Jeffers 4422-11.	R12	sim to Jeffers 4411-13.		
Sim to Jeffers 4411-10. L105LL 7488079P6	R12	sim to Jeffers 4411-12. Choke, RF: 1.50 µh ±10%, 0.50 ohms DC res max;	7488079 P 7	L104M
Sim to Jeffers 4411-10.	R12	sim to Jeffers 4411-10.	7488079P7	L104H
Choke, RF: 0.68 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4411-5.	R12	sim to Jeffers 4411-10. Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max;	7488079P6	L105LL
Sim to Jeffers 4411-5.	R12	sim to Jeffers 4411-8,		
Sim to Jeffers 4411-4.	R12	sim to Jeffers 4411-5.		L105L
Sim to Jeffers 4411-3. Sim to Jeffers 4411-3. Choke, RF: 10.0 µh ±10%, 0.60 ohms DC res max; sim to Jeffers 4421-7. Choke, RF: 39.0 µh ±10%, 2.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 2.00 ohms DC res max; sim to Jeffers 4422-11. Choke, RF: 39.0 µh ±10%, 2.00 ohms DC res max; sim to Jeffers 4422-11. PB219594P2 Contact strip: 8 pins. Contact strip: 9 pins. In REV C and earlier: 194115330P1 Silicon, NPN. Silicon, NPN. Silicon, NPN. Silicon, NPN. Earlier than REV A: 194115330P1 Silicon, NPN. Earlier than REV A: 194115328P1 Silicon, NPN. Silicon, NPN. Silicon, NPN. Composition: 560 ohms ±10%, 1/2 w. Composition: 560 ohms ±10%, 1/2 w. Composition: 560 ohms ±5%, 1/4 w. In REV C and earlier:	R12	sim to Jeffers 4411-4.		
Sim to Jeffers 4421-7.	R12	sim to Jeffers 4411-3.		
Choke, RF: 39.0 µh ±10%, 2.00 ohms DC res max; sim to Jeffers 4422-11.	R13	Choke, RF: 10.0 μ h \pm 10%, 0.60 ohms DC res max; sim to Jeffers 4421-7.	7488079P16	
Sim to Jeffers 4422-11."	R13	·		1
Includes: 19B219594P2 Contact strip: 8 pins. 19B219594P3 Contact strip: 9 pins.	R13	Choke, RF: 39.0 µh ±10%, 2.00 ohms DC res max; sim to Jeffers 4422-11.	7488079 P 50	L108
19B219594P2 Contact strip: 8 pins. 19B219594P3 Contact strip: 9 pins.	R13			
19B219594P3 Contact strip: 9 pins.	R13	Includes:		P902
Q101* 19A115330P1 Silicon, NPN. In REV C and earlier: 19A115330P1 Silicon, NPN; sim to Type 2N3906. Q102 thru Q106 Q107* 19A115330P1 Silicon, NPN. Earlier than REV A: 19A115330P1 Silicon, NPN. Q108 19A115328P1 Silicon, NPN. Q109 19A115329P2 Silicon, NPN. R101 3R77P561K Composition: 560 ohms ±10%, 1/2 w. In REV C and earlier:	R13	Contact strip: 8 pins.	19B219594P2	
Q101*	R13	Contact strip: 9 pins.	19B219594P3	
In REV C and earlier: 19A115910P1 Silicon, NPN; sim to Type 2N3906. Q102 thru q106 Q107* 19A115330P1 Silicon, NPN. Earlier than REV A: 19A115330P1 Silicon, NPN. Q108 19A115328P1 Silicon, NPN. Q109 19A115329P2 Silicon, NPN.	R13	1		
19A115910P1 Silicon, NPN; sim to Type 2N3906.	R14		19A115330P1	Q101*
Q102	R14			
thru Q106 Q107* 19A115328P1 Silicon, NPN. Earlier than REV A: 19A115330P1 Silicon, NPN. Q108 19A115328P1 Silicon, NPN. Q109 19A115329P2 Silicon, NPN.	R14			
Q107*	R14	Silicon, NPN.	19A115330P1	thru
19A115330P1 Silicon, NPN.	R14	Silicon, NPN.	19A115328Pl	l
Q108	R14	Earlier than REV A:	!	
Q109 19Al15329P2 Silicon, NPN.	R14	Silicon, NPN.	19A115330P1	
Q109 19A115329P2 Silicon, NPN.	R14	Silicon, NPN.		Q108
R101 3R77P561K Composition: 560 ohms ±10%, 1/2 w. R102* 3R152P682J Composition: 6800 ohms ±5%, 1/4 w. In REV C and earlier:	R14	Silicon, NPN.	19A115329P2	l
R102* 3R152P682J Composition: 6800 ohms ±5%, 1/4 w. In REV C and earlier:	R14 R14	RESISTORS		
In REV C and earlier:	R14	Composition: 560 ohms ±10%, 1/2 w.	3R77P561K	R101
	R14	Composition: 6800 ohms ±5%, 1/4 w.	3R152P682J	R102*
	R14 thr R15		207702027	
	R15	Composition: 39,000 ohms ±10%, 1/2 w.	3R77P393K	P100
R103 3R77P471K Composition: 470 ohms ±10%, 1/2 w.	i			l
R104 3R77P680K Composition: 68 ohms ±10%, 1/2 w. R105 3R77P221K Composition: 220 ohms ±10%, 1/2 w.	R15			

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	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.
	R106	3R77P102K	Composition: 1000 ohms $\pm 10\%$, $1/2$ w.		
ı	R107	3R77P153K	Composition: 15,000 ohms ±10%, 1/2 w.	TIOILL	19D416635G10
	R108	3R77P474K	Composition: 470,000 ohms ±10%, 1/2 w.	1	5493185P13
	R109	3R77P104K	Composition: 0.10 megohm ±10%, 1/2 w.	TlOIL	19D416635G10
	R110	3R77P223K	Composition: $22,000$ ohms $\pm 10\%$, $1/2$ w.		5493185P13
	R111	3R77P750J	Composition: 75 ohms ±5%, 1/2 w.	T101M	19D416635G2
	R112	3R77P681K	Composition: 680 ohms ±10%, 1/2 w.		5493185P13
	R113	3R77P332K	Composition: 3300 ohms ±10%, 1/2 w.	т101н	19D416635G2
	R114	3R77P511J	Composition: 510 ohms ±5%, 1/2 w.		5493185P13
١	R115	3R77P473K	Composition: 47,000 ohms ±10%, 1/2 w.	T102LL	19D416635G11
	R116	3R77P561K	Composition: 560 ohms $\pm 10\%$, $1/2$ w.	į	5493185P13
l	R117	3R77P821K	Composition: 820 ohms ±10%, 1/2 w.	T102L	19D416635G11
	R118	3R77P222K	Composition: 2200 ohms ±10%, 1/2 w.		5493185P13
١	R119	3R77P681K	Composition: 680 ohms ±10%, 1/2 w.	T102M	19D416635G3
	R1 20	3R77P511J	Composition: 510 ohms ±5%, 1/2 w.	1	5493185P13
١	R121	3R77P223K	Composition: 22,000 chms ±10%, 1/2 w.	т102н	19D416635G3
	R122	3R77P153K	Composition: 15,000 ohms ±10%, 1/2 w.		5493185P13
١	and R123		, =,, =, =, = ,,	T103LL	19D416635G12
1	R124	3R77P223K	Composition: 22,000 ohms ±10%, 1/2 w.	1	5493185P13
ļ	R125	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.	T103L	19D416635G12
١	R126	3R77P391K	Composition: 390 ohms ±10%, 1/2 w.		5493185P13
	R127	19B209358P106	Variable, carbon film: approx 75 to 10,000 ohms ±10%, 0.25 w; sim to CTS Type X-201.	T103M	19D416635G4
	R128	19B209358P108	Variable, carbon film: approx 100 to 50,000 ohms $\pm 10\%$, 0.25 w; sim to CTS Type X-201.	т103н	5493185P13 19D416635G4
	R129	3R77P750J	Composition: 75 ohms ±5%, 1/2 w.		5493185P13
	R130	3R77P681K	Composition: 680 ohms ±10%, 1/2 w.	T104LL	19D416635G13
١	R131	3R77P332K	Composition: 3300 ohms $\pm 10\%$, $1/2$ w.		5493185P13
	R132	3R77P511J	Composition: 510 ohms ±5%, 1/2 w.	T104L	19D416635G13
	R133	3R77P473K	Composition: 47,000 ohms ±10%, 1/2 w.		5493185P13
	R134	3R77P561K	Composition: 560 ohms ±10%, 1/2 w.	T104M	19D416635G5
	R135	3R77P223K	Composition: 22,000 ohms ±10%, 1/2 w.		5493185P13
	R136	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.	T104H	19D416635G5
-	R137	3R77P330K	Composition: 33 ohms ±10%, 1/2 w.		5493185P13
	R138	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.	T105LL	19D416635G13
	R139	3R77P121K	Composition: 120 ohms ±10%, 1/2 w.		5493185P13
	R140	3R77P220K	Composition: 22 ohms ±10%, 1/2 w.	T105L	19D416635G13
-	R141	3R77P680K	Composition: 68 ohms ±10%, 1/2 w.		5493185P13
	R142	3R77P220K	Composition: 22 ohms ±10%, 1/2 w.	T105M	19D416635G5
١	R143LL	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.	1	5493185P13
	R143L	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.	т105н	19D416635G5
-	R143M	3R77P820K	Composition: 82 ohms ±10%, 1/2 w.		5493185P13
1	R143H	3R77P820K	Composition: 82 ohms ±10%, 1/2 w.	T106LL	19D416635G14
	R144LL	3R77P150K	Composition: 15 ohms ±10%, 1/2 w.		5493185P13
	R144L	3R77P150K	Composition: 15 ohms ±10%, 1/2 w.	T106L	19D416635G14
	R144M	3R77P100K	Composition: 10 ohms $\pm 10\%$, $1/2$ w.		5493185P13
	R144H	3R77P100K	Composition: 10 ohms ±10%, 1/2 w.	T106M	19D416635G6
ļ	R145	3R77P333K	Composition: 33,000 ohms $\pm 10\%$, $1/2$ w.		5493185P13
	R146	3R77P683K	Composition: 68,000 ohms ±10%, 1/2 w.	т106н	19D416635G6
	R147	3R77P333K	Composition: 33,000 ohms ±10%, 1/2 w.		5493185P13
	thru R150			T107LL	19D416635G15
-	R151	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.	`	5493185P13
-	R152	3R77P100K	Composition: 10 ohms ±10%, 1/2 w.	T107L	19D416635G15
- 1	1	l		1	

Composition: 1000 ohms ±10%, 1/2 w.

3R77P102K

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.
T101LL	19D416635G10	TRANSFORMER	Т107М	19D416635G7

Tuning slug,

Tuning slug.

Coil. Includes:

Coil. Includes:

Tuning slug.

Tuning slug.

Coil. Includes:

Tuning slug.

Tuning slug,

Tuning slug.

Tuning slug.

Tuning slug.

Coil. Includes:

Tuning slug,

Tuning slug.

Tuning slug.

Tuning slug.

5493185P13

Coil, Includes:

Coil. Includes:

Coil, Includes:

Coil. Includes:

Coil. Includes:

Coil. Includes:

Coil, Includes:

Coil. Includes:

Coil. Includes:

Coil, Includes:

	T107M	19 D41 6635 G 7	Coil. Includes:
		5493185P13	Tuning slug.
	Т107Н	19D416635G7	Coil. Includes:
		5493185P13	Tuning slug.
,	T108LL	19 D4 16635 G 16	Coil. Includes:
		5493185P13	Tuning slug.
	T108L	19D416635G16	Coil. Includes:
		5493185P13	Tuning slug.
	T108M	19D416635G8	Coil. Includes:
		5493185P13	Tuning slug.
	т108Н	19D416635G8	Coil. Includes:

XY101 thru XY108

19A116779P1

19A129393G13

19A129393G16

19B219619P1

19A121252P1

19A129424G2

4036555P1

4029006P3

	5493185P13	Tuning slug.
Н	19D416635G7	Coil. Includes:
	5493185P13	Tuning slug.
LL	19D416635G16	Coil. Includes:
	5493185P13	Tuning slug.
L	19D416635G16	Coil. Includes:
	5493185P13	Tuning slug.
M	19D416635G8	Coil. Includes:
	5493185P13	Tuning slug.
H	19D416635G8	Coil. Includes:
	5493185P13	Tuning slug.
	19A116842P1	Frequency Divider: sim to Texas Instrument Type SN54H73N.
	19D416542G1	Transmitter, Audio.
1	4036887P56	Silicon, Zener.
		SOCKETS
		NOTE: When reordering, specify quantity.
		norm. "men reordering, specify quantity,

DESCRIPTION

Contact, electrical; sim to Molex 08-54-0404.

NOTE: When reordering specify ICOM Frequency.
ICOM Freq = (Operating Freq)

Externally Compensated: 5 PPM, 25-50 MHz.

Can. (Used with T101-T108 and L101-L103).

Insulator, washer: nylon. (Used with Q109).

Clip, compression: 0.375 x 0.19 x .02 inches, sim to Tinnerman Products Inc. C5426-014-24. (Used with Q109).

Compensated: 2 PPM, 25-50 MHz.

Heat sink, (Used with Q109).

Shield.

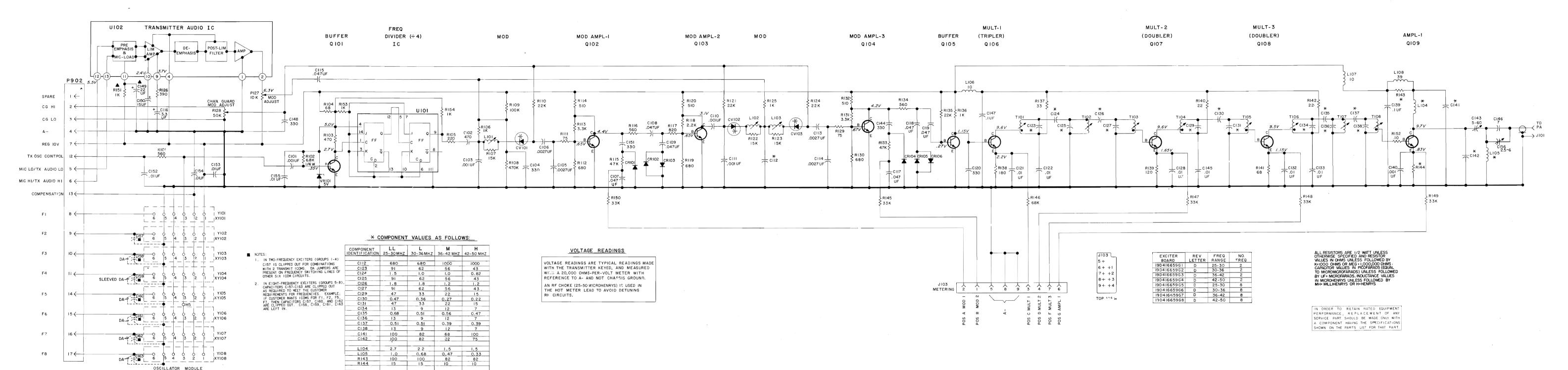
Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for description of parts aff affected by these revisions.

PRODUCTION CHANGES

LBI-4896

REV. A - D: - Exciter Board 19D416659G1-8. Incorporated in initial shipment

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.



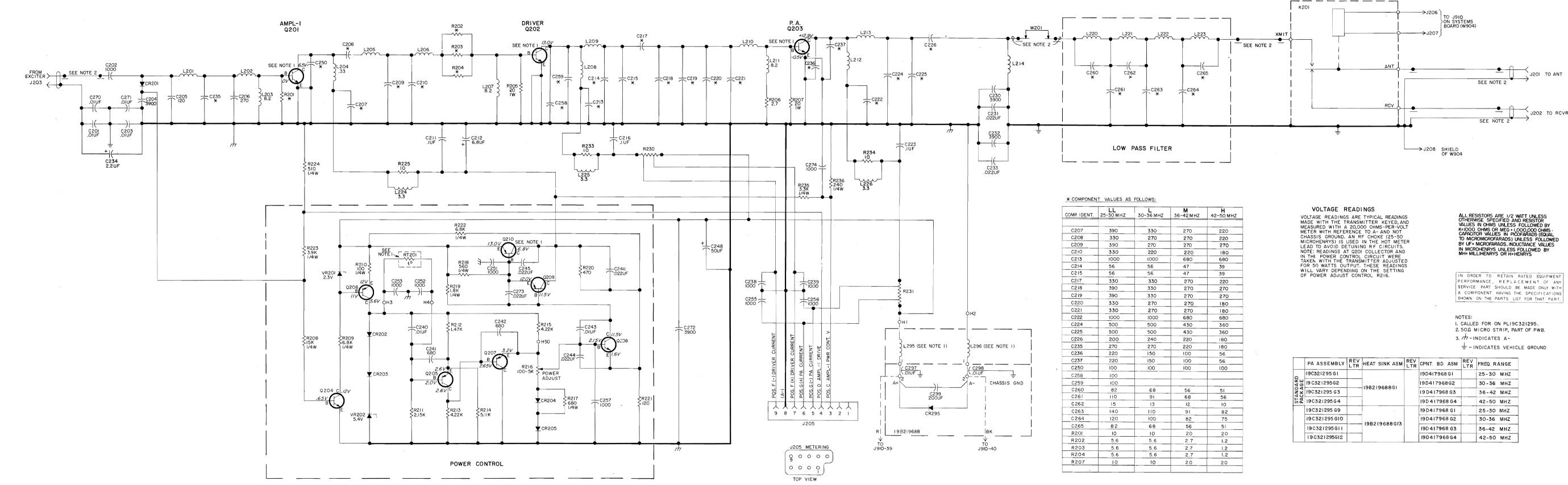
(19R621827, Rev. 12)

SCHEMATIC DIAGRAM

25-50 MHz, EXCITER BOARD 19D416659G1-8

▲ THESE COMPONENTS NOT PRESENT ON 2ND EXCITER IN WIDE SPACE XMTR COMBINATIONS.

4 Issue 1



(19R622106, Rev. 0)

SCHEMATIC DIAGRAM

25-50 MHz, 50-WATT POWER AMPLIFIER 19C321295G1-4 & G9-12

PARTS LIS	Т
LBI-4897	
25-50 MHz, 50 POWER AMPLI	WAT FIEF

POWER AMPLIFIER 19C321295G1-G4 19C321295G9-G12						
SYMBOL	GE PART NO.	DESCRIPTION				
	•	19C321295G1, C9 25-30 MHz (LL) 19C321295G2, G10 30-36 MHz (L) 19C321295G3, G11 36-42 MHz (M) 19C321295G4, G12 42-50 MHz (H)				
L295 and L296	19A129356P1	Coil.				
Q201	19A116839P1	TRANSISTORS				
Q202	19Al16839P2	Silicon, NPN.				
Q203	19A116839P3	Silicon, NPN.				
Q210	19A116375P1	Silicon, PNP.				
RT201	19A129379G1	Thermistor.				
		POWER AMPLIFIER BOARD 19D416700G1 25-30 MHz 19D416700G2 30-36 MHz 19D416700G3 36-42 MHz 19D416700G4 42-50 MHz				
C201	19All6080Pl01	CAPACITORS				
C202	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.				
C203	19Al16080P101	Polyester: 0.01 µf ±10%, 50 VDCW.				
C204	19116655P23	Ceramic disc: 3900 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.				
C205	7489162P29C	Silver mica: 120 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C206	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C207LL	7489162P41C	Silver mica: 390 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C207L	7489162P39C	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C207M	7489162P37C	Silver mica: 270 pf $\pm 5\%$, 500 VDCW; sim to Electro Motive Type DM-15.				
C207H	7489162P35C	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C208LL	7489162P39C	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C208L and C208M	7489162P37C	Silver mica: 270 pf $\pm 5\%$, 500 VDCW; sim to Electro Motive Type DM-15.				
C208H	7489162P35C	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C209LL	7489162P41C	Silver mica: 390 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C209L	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C209M	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
С209Н	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C210LL	7489162P39C	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				

SYMBOL	GE PART NO.	DESCRIPTION				
C210L and C210M	7489162P35C	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
С210н	7489162P33C	Silver mica: 180 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C211	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.				
C212	5496267P18	Tantalum: 6.8 μf ±20%, 35 VDCW; sim to Sprague Type 150D.				
C213LL and C213L	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.				
C213M and C213H	19All6655P17	Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.				
C214LL and C214L	19A116656P56J0	Ceramic disc: 56 pf $\pm 5\%$, 500 VDCW, temp coef 0 PPM.				
C214M	19All6656P47J0	Ceramic disc: 47 pf ±5%, 500 VDCW, temp coef 0 PPM.				
С214Н	19A116656P39J0	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef 0 PPM.				
C215LL and C215L	19A116656P56J0	Ceramic disc: 56 pf $\pm 5\%$, 500 VDCW; temp coef 0 PPM.				
C215M	19A116656P47J0	Ceramic disc: 47 pf ±5%, 500 VDCW, temp coef 0 PPM.				
С215Н	19A116656P39J0	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef 0 PPM.				
C216	19Al16080P107	Polyester: 0.1 µf ±10%, 50 VDCW.				
C217LL and C217L	7489162P39C	Silver mica: 470 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C217M	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
С217Н	7489162P35C	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C218LL	7489162P41C	Silver mica: 390 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C218L	7489162P39C	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C218M and C218H	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C219LL	7489162P41C	Silver mica: 390 pf i5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C219L	7489162P39C	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C219M and C219H	7489162P37C	Silver mica: 270 pf $\pm 5\%$, 500 VDCW; sim to Electro Motive Type DM-15.				
C220LL	7489162P39C	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C220L and C220M	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
С220Н	7489162P33C	Silver mica: 180 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C221LL	7489162P39C	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C221L and C221M	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
С221Н	7489162P33C	Silver mica: 180 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.				
C222LL and C222L	19All6655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.				
C222M and C222H	19A116655P17	Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.				
C 223	19Al16080Pl07	Polyester: 0.1 µf ±10%, 50 VDCW.				
C224LL and C224L	19A116679P500J	Mica: 500 pf ±5%, 250 VDCW.				

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL
C 224M	19A116679P430J	Mica: 430 pf ±5%, 250 VDCW.	C260L
C224H	19A116679P360J	Mica: 360 pf ±5%, 250 VDCW.	C260M
C225LL and C225L	19A116679P500J	Mica: 500 pf ±5%, 250 VDCW.	С260Н
C225M	19Al16679P430J	Mica: 430 pf ±5%, 250 VDCW.	C261LL
C225H	19A116679P360J	Mica: 360 pf ±5%, 250 VDCW.	C261L
C226LL	19A116679P200J	Mica: 200 pf ±5%, 250 VDCW.	C261M
C226L	19A116679P240J	Mica: 240 pf ±5%, 250 VDCW.	С261Н
C226M	19A116679P220J	Mica: 220 pf ±5%, 250 VDCW.	C262LL
С226Н	19A116679P180J	Mica: 180 pf ±5%, 250 VDCW.	C262L
C230	19A116655P23	Ceramic disc: 3900 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C262M
C231	19A116080P103	Polyester: 0.022 μf ±10%, 50 VDCW.	C262H
C232	19A116655P23	Ceramic disc: 3900 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.	C263LL C263L
C233	19A116080P103	Polyester: 0.022 μf ±10%, 50 VDCW.	C263M
C234	5496267P13	Tantalum: 2.2 μ f $\pm 20\%$, 20 VDCW; sim to Sprague Type 150D.	С263Н
C235LL	7489162P37C	Silver mica: 270 pf ±5%, 500 VDCW; sim to	C264LL
and C235L		Electro Motive Type DM-15.	C264L
C235M	7489162P35C	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C264M
С235Н	7489162P33C	Silver mica: 180 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C264H C265LL
C236LL	19Al16656P220J4	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -470 PPM.	C265L
C236L	19Al16656Pl50Jl	Ceramic disc: 150 pf ±5%, 500 VDCW, temp coef -150 PPM.	C265M C265H
C236M	19A116656P100J1	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef -150 PPM,	C270
С236Н	19A116656P56J0	Ceramic disc: 56 pf ±5%, 500 VDCW, temp coef 0 PPM.	C271
C237LL	19A116656P220J4	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef	C273
C237L	19A116656P150J1	Ceramic disc: 150 pf ±5%, 500 VDCW, temp coef -150 PPM.	. C274
C237M	19Al16656Pl00J1	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef -150 PPM.	
С237Н	19A116656P56J0	Ceramic disc: 56 pf ±5%, 500 VDCW, temp coef 0 PPM.	CR201 thru
C238 and C239	19A116655P19	Cermic disc: 1000 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.	CR205
C240	19A116080P101	Polyester: 0.01 µf ±10%, 50 VDCW.	J201 thru
C241 and C242	19All6655P17	Ceramic disc: 680 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.	J203 J205
C243	19Al16080P101	Polyester: 0.01 µf ±10%, 50 VDCW.	
C244 thru	19A116080P103	Polyester: 0.022 μf ±10%, 50 VDCW.	J206
C246 C248	19A115680P4	Electrolytic: 50 µf +150% -10%, 25 VDCW; sim	and J207
C250	19Al16656Pl00Jl	to Mallory Type TT. Ceramic disc: 100 pf ±6%, 500 VDCW, temp coef	J208
C251 thru	19Al16655P19	-150 PPM. Cermic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	K201
C253 C255 thru	19A116655P19	Ceramic disc: 1000 pf $\pm 20\%,$ 1000 VDCW; sim to RMC Type JF Discap.	
C257 C258LL	19Al16656P100K4	Ceramic disc: 100 pf ±10%, 500 VDCW, temp coef	L201LL L201L
C259LL	19A116656P100K4	-470 PPM. Ceramic disc: 100 pf \pm 10%, 500 VDCW, temp coef	L201M
		-470 PPM.	L201H
C 260LL	19Al16656P82J1	Ceramic, disc: 82 pf $\pm 5\%$, 500 VDCW, temp coef -150 PPM.	L202LL L202L

SYMBOL	GE PART NO.	DESCRIPTION	SYMB
C260L	19A116656P68J1	Ceramic, disc: 68 pf ±5%, 500 VDCW, temp coef	L202M
		-150 PPM.	L202H
C260M	19A116656P56J1	Ceramic, disc: 56 pf ±5%, 500 VDCW, temp coef -150 PPM.	L203
С260Н	19All6656P51J1	Ceramic, disc: 51 pf ±5%, 500 VDCW, temp coef -150 PPM.	L204
C261LL	19A116679P110J	Mica: 110 pf ±5%, 250 VDCW.	
C261L	19Al16679P91J	Mica: 91 pf ±5%, 250 VDCW.	L205LL and
C261M	19A116679P68J	Mica: 68 pf ±5%, 250 VDCW.	L205L
C261H	19A116679P56J	Mica: 56 pf ±5%, 250 VDCW.	L205M
C262LL	19A116656P15J1	Ceramic, disc: 15 pf ±5%, temp coef -150 PPM.	L205H
C262L	19A116656P13JI	Ceramic, disc: 13 pf ±5%, temp coef -150 PPM.	L206LL
C262M	19A116656P12J1	Ceramic, disc: 12 pf ±5%, temp coef -150 PPM.	L206L
C262H	19All6656Pl0Jl	Ceramic, disc: 10 pf ±0.5 pf, temp coef -50 PPM.	L206M
C263LL	19A116679P140J	Mica: 140 pf ±5%, 250 VDCW.	L208H
C263L	19A116679P110J	Mica: 110 pf ±5%, 250 VDCW.	L207
C263M	19A116679P91J	Mica: 91 pf ±5%, 250 VDCW.	L208LL
			and
C263H	19A116679P82J	Mica: 82 pf ±5%, 250 VDCW,	L208L
C264LL	19A116679P120J	Mica: 120 pf ±5%, 250 VDCW.	L208M and
C264L	19A116679P100J	Mica: 100 pf ±5%, 250 VDCW.	L208H
C264M	19A116679P82J	Mica: 82 pf ±5%, 250 VDCW.	L209LL
C264H	19A116679P75J	Mica: 75 pf ±5%, 250 VDCW.	L209L and
C265LL	19A116656P82J1	Ceramic, disc: 82 pf ±5%, temp coef -150 PPM.	L209M
C265L	19A116656P68J1	Ceramic, disc: 68 pf $\pm 5\%$, temp coef -150 PPM.	L209H
C265M	19Al16656P56J1	Ceramic, disc: 56 pf ±5%, temp coef -150 PPM.	L210LL
C265H	19A116656P51J1	Ceramic, disc: 51 pf ±5%, temp coef -150 PPM.	L210L
C270 and	19A116080P101	Polyester: 0.01 μf ±10%, 50 VDCW.	L210M
C271			L210H
C272	19A116655P23	Ceramic disc: 3900 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	L211
C273	19A116080P103	Polyester: 0.022 μf ±10%, 50 VDCW.	L212LL
C274	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	L212L
		DIODES AND RECTIFIERS	and L212H
CR201	19A115250Pl	Silicon.	L213LL
thru CR205			L213L
		JACKS AND RECEPTACLES	L213M
J 201	19A116832P1	Receptacle, coaxial: jack type; sim to Cinch	L213H
thru J203		14H11613.	L214LL
J205	19B219374G1	Connector, Includes:	L214L
•	19C317957P1	Shell.	L214M
	19A116651P1	Contact, electrical: sim to Malco XO-2864.	L214H
J206		(Part of K201).	L220LL
and J 207		,	L220L
	403351384	Contact electrical, sim to Bood Chair 100 0	L220L
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	L220M
		RELAYS	i
K201	19A116722P1	Relay, hermetic sealed: 13.6 VDC ±20%, 125 ohms	L221LL
		coil res, 1 form C contact.	L221L
		INDUCTORS	L221M
L201LL	19A129347P2	Coil.	L221H
L201L	19A129347Pl	Coil.	L222LL
L201M	19A129347P3	Coil.	L222L
L201H	19A129347P4	Coil.	L222M
L202LL	19A129352P9	Coil.	L222H
L202L	19A129354P4	Coil.	L223LL
		1	1

19A129	9352P7 79P42 79P3 9351P3 9351P2 9351P2 9352P1 9352P1 9352P3 9348P2 99P42	Coil. Coil. Choke, RF: 8.20 µh ±10%, 0.25 ohms DC res max; sim to Jeffers 4422-3. Choke, RF: 0.33 µh ±20%, 0.07 ohms DC res max; sim to Jeffers 4411-3. Coil.	L223L L223M L223H L224 L225 and L226 Q204 Q205 thru Q207 Q208 Q209	19A129360P6 19A129360P4 19A129360P1 7488079P10 19A129346G1 19A115910P1 19A115768P1 19A115910P1 19A115910P1 19A115910P1	Coil. Coil. Coil. Choke, RF: 3.30 µh ±10%, 0.15 ohms DC sim to Jeffers 4421-1. Coil.
19A129	79P42 79P3 3351P3 3351P2 3351P2 3352P1 3352P1 3352P1 3352P3 348P2 79P42 349P1	Choke, RF: 8.20 µh ±10%, 0.25 ohms DC res max; sim to Jeffers 4422-3. Choke, RF: 0.33 µh ±20%, 0.07 ohms DC res max; sim to Jeffers 4411-3. Coil.	L223M L223H L224 L225 and L226 Q204 Q205 thru Q207 Q208	19A129360P1 7488079P10 19A129346G1 19A115910P1 19A115768P1 19A115910P1	Coil. Coil. Choke, RF: 3,30 µh ±10%, 0.15 ohms DC sim to Jeffers 4421-1. Coil.
.2003 748807 .2004 748807 .2005L 19A129 .2005L 19A129 .2005L 19A129 .2006L 19A129 .2006L 19A129 .2006L 19A129 .2006L 19A129 .2006L 19A129 .2008L 19A129 .2008L 19A129 .2008L 19A129 .2009L 19A129 .2009L 19A129 .2016L 19A129 .2106L 19A129 .211 19A129 .211 19A129 .2126L 19A129 .211 19A129 .2126L 19A129 .211 19A129 .2126L 19A129 .2127 .2128L 19A129 .2138L 19A129 .2146L 19A129 .2126L 19A129 .2216L 19A129 .2216L 19A129 .2216L 19A129 .2216L 19A129 .2216L 19A129 .2220L 19A129 .2220L 19A129 .2220L 19A129 .2220L 19A129 .2220L 19A129 .2220L 19A129 .2221L 19A129	79P42 79P3 3351P3 3351P2 3351P2 3352P1 3352P1 3352P1 3352P3 348P2 79P42 349P1	Choke, RF: 8.20 µh ±10%, 0.25 ohms DC res max; sim to Jeffers 4422-3. Choke, RF: 0.33 µh ±20%, 0.07 ohms DC res max; sim to Jeffers 4411-3. Coil.	L223H L224 L225 and L226 Q204 Q205 thru Q207 Q208	19A129360P1 7488079P10 19A129346G1 19A115910P1 19A115768P1 19A115910P1	Coil. Choke, RF: 3,30 µh ±10%, 0.15 ohms DC sim to Jeffers 4421-1. Coil.
.205LL 19A129 .205L 19A129 .205L 19A129 .206L 19A129 .206L 19A129 .206L 19A129 .206H 19A129 .206H 19A129 .206H 19A129 .207 748807 .208LL 19A129 .208L 19A129 .208L 19A129 .209L 19A129 .209H 19A129 .210L 19A129 .210L 19A129 .210L 19A129 .211 748807 .212L 19A129 .212L 19A129 .212L 19A129 .213L 19A129 .213L 19A129 .213L 19A129 .214L 19A129 .214H 19A129 .220L 19A129 .220L 19A129 .220L 19A129 .220L 19A129 .221L 19A129 .2220L 19A129 .2220L 19A129 .2220L 19A129 .2221L 19A129	0351P3 0351P2 0351P2 0352P1 0352P1 0352P3 0348P2 09P42 0349P1	sim to Jeffers 4422-3. Choke, RF: 0.33 µh ±20%, 0.07 ohms DC res max; sim to Jeffers 4411-3. Coil. L225 and L226 Q204 Q205 thru Q207	19A129346G1 19A115910P1 19A115768P1 19A115910P1	sim to Jeffers 4421-1. Coil. TRANSISTORS Silicon, NPN; sim to Type 2N3904. Silicon, PNP; sim to Type 2N3702. Silicon, NPN; sim to Type 2N3904.	
and 2205L 19A129 2206L 19A129 22	0351P2 0351P2 0352P1 0352P1 0352P3 0348P2 09P42 0349P1	Coil. Choke, RF: 8.20 µh ±10%, 0.25 ohms DC res max; sim to Jeffers 4422-3.	Q204 Q205 thru Q207 Q208	19A115910P1 19A115768P1 19A115910P1	Silicon, NPN; sim to Type 2N3904. Silicon, PNP; sim to Type 2N3702. Silicon, NPN; sim to Type 2N3904.
19A129	9351P2 9352P1 9352P1 9352P3 9348P2 9942 9942 9349P1	Coil. Coil. Coil. Coil. Coil. Coil. Coil. Choke, RF: 8.20 µh ±10%, 0.25 ohms DC res max; sim to Jeffers 4422-3.	Q204 Q205 thru Q207 Q208	19A115768P1 19A115910P1	Silicon, NPN; sim to Type 2N3904, Silicon, PNP; sim to Type 2N3702. Silicon, NPN; sim to Type 2N3904.
19A129	9351P2 9352P1 9352P1 9352P3 9348P2 9942 9942 9349P1	Coil. Coil. Coil. Coil. Coil. Coil. Coil. Choke, RF: 8.20 µh ±10%, 0.25 ohms DC res max; sim to Jeffers 4422-3.	Q205 thru Q207 Q208	19A115768P1 19A115910P1	Silicon, NPN; sim to Type 2N3904, Silicon, PNP; sim to Type 2N3702. Silicon, NPN; sim to Type 2N3904.
19A129 1	9352P1 9352P1 9352P3 9348P2 9942 9942 9349P1	Coil. Coil. Coil. Coil. Coil. Choke, RF: 8.20 μh $\pm 10\%$, 0.25 ohms DC res max; sim to Jeffers 4422-3.	Q205 thru Q207 Q208	19All5910Pl	Silicon, PNP; sim to Type 2N3702. Silicon, NPN; sim to Type 2N3904.
19A129 1	9352P1 9352P3 9348P2 9942 9349P1	Coil. Coil. Coil. Choke, RF: 8.20 μh $\pm 10\%$, 0.25 ohms DC res max; sim to Jeffers 4422-3.	Q207 Q208	19All5910Pl	Silicon, NPN; sim to Type 2N3904.
19A129 1	3352P3 3348P2 99P42 3349P1	Coil. Coil. Choke, RF: 8.20 μh $\pm 10\%,~0.25$ ohms DC res max; sim to Jeffers 4422-3.	Q208		
19A129	348P2 9P42 349P1 349P2	Coil. Choke, RF: 8.20 μh $\pm 10\%$, 0.25 ohms DC res max; sim to Jeffers 4422-3.	Q209	19A129187P1	
19A129 1	9942 9349P1 9349P2	Choke, RF: 8.20 μh $\pm 10\%,$ 0.25 ohms DC res max; sim to Jeffers 4422-3.			Silicon, PNP.
19A129 1	9349P1 9349P2	sim to Jeffers 4422-3.	l I		
nd	3 4 9P2	Coil	R201LL	3R77P100J	
19A129 1		2011.	and R201L	387791003	Composition: 10 ohms ±5%, 1/2 w.
19A129 1	355P1	Coil.	R201M and R201H	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.
.nd .2009M .2009M .2009M .210LL .210LL .2110M .210H .2110H .212H .212L .212LL .212LL .212L .212L .212H .213LL .213LL .213LL .213LL .213LL .214LL .222LL .2220LL .2220LL .2220LL .2220LL .2220LL .2221LL .2221LL .2221LL .2221LL .2221LL .2221LL .2221LL .2221L .22221L .22221L .22221L .222221L .222221L .2222222222		Coil.	R202LL and	5490205P6	Composition: 5.6 ohms ±5%, 1 w.
19A129 19A1	352P4	Coil.	R202L		
19A129 1			R202M	5490205P16	Composition: 2.7 ohms ±5%, 1 w.
.210L 19A129210M 19A129210H 19A129211 748807212LL 19A129212L 19A129212H 19A129213L 19A129213L 19A129213H 19A129214L 19A129214L 19A129214L 19A129214H 19A129224H 19A129220L 19A129220L 19A129220L 19A129220H 19A129220H 19A129220H 19A129220H 19A129220H 19A129221LL 19A129.	352P2	Coil.	R202H	7147161P22	Composition: 1.2 ohms ±5%, 1/2 w.
19A129	358P1	Coil.	R203LL and	5490205P6	Composition: 5.6 ohms ±5%, 1 w.
.210H 19A129 .211 748807 .212LL 19A129 .212L 19A129 .212H 19A129 .213L 19A129 .213L 19A129 .213L 19A129 .213H 19A129 .214L 19A129 .214L 19A129 .214L 19A129 .214L 19A129 .214L 19A129 .214L 19A129 .220L 19A129 .220L 19A129 .220L 19A129 .220H 19A129 .220H 19A129 .220H 19A129 .220H 19A129 .221L 19A129	359 P 1	Coil.	R203L		
211 748807 212LL 19A129 212L 19A129 212H 19A129: 213L 19A129: 213L 19A129: 213L 19A129: 213H 19A129: 214L 19A129: 214L 19A129: 214H 19A129: 224H 19A129: 220L 19A129: 220L 19A129: 220L 19A129: 220H 19A129: 220H 19A129: 221L 19A129:	357P1	Coil.	R203M	5490205P16	Composition: 2.7 ohms ±5%, 1 w.
2212LL 19A129 2212L 19A129 2212L 19A129 2213L 19A129 2213L 19A129 2213L 19A129 2213H 19A129 2214L 19A129 2214L 19A129 2214L 19A129 2214L 19A129 220L 19A129 220L 19A129 220L 19A129 220H 19A129 220H 19A129 221L 19A129	357P2	Coil.	R203H	7147161P22	Composition: 1.2 ohms ±5%, 1/2 w.
nd .212M	9942	Choke, RF: 8.20 μh ±10%, 0.25 ohms DC res max; sim to Jeffers 4422-3.	R204LL and R204L	5490205P6	Composition: 5.6 ohms ±5%, 1 w.
19A129: 212L	349Pl	Coil.	R204M	5490205P16	Composition: 2.7 ohms ±5%, 1 w.
nd 212H 19A129: 213L 19A129: 213L 19A129: 213M 19A129: 213H 19A129: 214L 19A129: 214L 19A129: 220LL 19A129: 220L 19A129: 220M 19A129: 220H 19A129: 220H 19A129: 220H 19A129: 220H 19A129: 221LL		·	R204H	7147161P22	Composition: 1.2 ohms ±5%, 1/2 w.
19A129: 213LL	349P2	Coil.	R205	3R78P200J	Composition: 20 ohms ±5%, 1 w.
.213L 19A129: .213M 19A129: .213H 19A129: .214LL 19A129: .214L 19A129: .214H 19A129: .220L 19A129: .220L 19A129: .220M 19A129: .220H 19A129: .221L 19A129: .221L 19A129:			R206	7147161P6	Composition: 2.7 ohms ±5%, 1/2 w.
.213M 19A129: .213H 19A129: .214LL 19A129: .214L 19A129: .214H 19A129: .220LL 19A129: .220L 19A129: .220L 19A129: .220M 19A129: .220H 19A129: .221LL 19A129:	351P1	Coil,	R207LL	3R78P100J	Composition: 10 ohms ±5%, 1 w.
.213H 19A129: .214L 19A129: .214L 19A129: .214M 19A129: .224H 19A129: .220L 19A129: .220L 19A129: .220M 19A129: .220H 19A129: .221L 19A129: .221L 19A129:	358P2	Coil.	and R207L		
.214LL 19A129: .214L 19A129: .214M 19A129: .214H 19A129: .220LL 19A129: .220L 19A129: .220M 19A129: .220H 19A129: .221LL 19A129:	355 P 3	Coil.	R207M	3R78P200J	Composition: 20 ohms ±5%, 1 w.
.214L 19A129 .214M 19A129 .214H 19A129 .220LL 19A129 .220L 19A129 .220M 19A129 .220H 19A129 .221LL 19A129	351P4	Coil.	and R207H		
.214M 19A129224H 19A129220LL 19A129220L 19A129220M 19A129220H 19A129221LL 19A129.	353P3	Coil.	R208	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.
.214H 19A129 .220LL 19A129 .220L 19A129 .220M 19A129 .220H 19A129 .221LL 19A129	355P5	Coil.	R209	3R152P682J	Composition: 6800 ohms ±5%, 1/4 w.
.220LL 19A129: .220L 19A129: .220M 19A129: .220H 19A129: .221LL 19A129:	355P4	Coil.	R210	3R152P101J	Composition: 100 ohms ±5%, 1/4 w.
.220L 19A129. .220M 19A129. .220H 19A129. .221LL 19A129.	352P10	Coil.	R211	19A116278P233	Metal film: 2150 ohms $\pm 2\%$, $1/2$ w.
.220M 19A129: .220H 19A129: .221LL 19A129:	360P9	Coil.	R212	19A116278P217	Metal film: 1470 ohms ±2%, 1/2 w.
.220H 19A129. .221LL 19A129. .221L 19A129.	360P6	Coil.	R213	19A116278P261	Metal film: 4220 ohms $\pm 2\%$, $1/2$ w.
.221LL 19A129:	360P4	Coil.	R214	19A116278P269	Metal film: 5110 ohms ±2%, 1/2 w.
221L 19A129	360P1	Coil.	R215	19A116278P261	Metal film: 4220 ohms ±2%, 1/2 w.
l l	360P10	Coil.	R216	19A116559P102	Variable, cermet: 5000 ohms ±20%, .5
.221M 19A129	360P7	Coil.	2019	ani sancai t	CTS Series 360.
	360P3	Coil.	R217	3R152P681J	Composition: 680 ohms ±5%, 1/4 w.
221H 19A129	360P2	Coil.	R218	3R152P561J	Composition: 560 ohms ±5%, 1/4 w.
222LL 19A129	26021	Coil.	R219	3R152P182J	Composition: 1800 ohms ±5%, 1/4 w.
222L 19A129	COOLIT	Coil.	R220	3R77P471J	Composition: 470 ohms ±5%, 1/2 w.
.222M 19A129		Coil.	R221	3R77P121J	Composition: 120 ohms ±5%, 1/2 w.
.222H 19A129	360P8	Coil.	R222	3R152P682J	Composition: 6800 ohms ±5%, 1/4 w.
.223LL 19A129	360P8 360P5	Coil.	R223 R224	3R152P392J	Composition: 3900 ohms ±5%, 1/4 w.

DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
Coil.	R225	3R77P100J	Composition: 10 ohms ±5%, 1/2 w.
Coil.	R230	19C320212P2	Shunt resistor.
Coil.	and R231	13032021272	Shall Teststor.
Choke, RF: 3.30 μh ±10%, 0.15 ohms DC res max;	R233	3R78P100K	Composition: 10 ohms ±10%, 1 w.
sim to Jeffers 4421-1.	and R234	ow.orrow	composition. To omis ito,, i w.
Coil.	R235	3R152P332J	Composition: 3300 ohms ±5%, 1/4 w.
	R236	3R152P241J	Composition: 240 ohms ±5%, 1/4 w.
TRANSISTORS	1230	3R102F2410	Composition. 240 offins 15%, 1/4 w.
Silicon, NPN; sim to Type 2N3904.			
Silicon, PNP; sim to Type 2N3702.	VR201	4036887P1	Silicon, Zener.
	VR 202	4036887P5	Silicon, Zener.
Silicon, NPN; sim to Type 2N3904.			
Silicon, PNP.	W201	19A129571P1	Wire strap,
RESISTORS	,,201	IOMIZOUTIFI	"ITE Strap,
Composition: 10 ohms ±5%, 1/2 w.			HEAT SINK ASSEMBLY
			19B219688GI M MODEL AND INTERMITTANT DUTY STATION 19B219688GI3 E MODEL
Composition: 20 ohms ±5%, 1/2 w.			198219088013 E MODEL
·			
Composition: 5.6 ohms ±5%, 1 w.	C297 and	19Al16708Pl	Ceramic, feed-thru: 0.01 μf +100% -0%, 500 VDCW;
,	C298		sim to Erie Style 327.
Composition: 2.7 ohms ±5%, 1 w.	C299	19A115680P10	Electrolytic: 200 µf +150% -10%, 18 VDCW; sim
Composition: 1.2 ohms ±5%, 1/2 w.			to Mallory Type TT.
Composition: 5.6 ohms ±5%, 1 w.			DIODES AND RECTIFIERS
	CR295	19Al16783Pl	Silicon.
Composition: 2.7 ohms ±5%, 1 w.			
Composition: 1.2 ohms ±5%, 1/2 w.			MISCELLANEOUS
Composition: 5.6 ohms ±5%, 1 w,		19B219391P1	Filter casting.
- ", - '		19D416712P1	Insulator. (Located under printed wiring board).
Composition: 2.7 ohms ±5%, 1 w.		5492178P2	Washer, spring tension.
Composition: 1.2 ohms ±5%, 1/2 w.		N207P15C6	Hex nut: No. 8-32. (Used with Q201 and Q202).
Composition: 20 ohms ±5%, 1 w.		N207P16C6	Hex nut: No. 10-32. (Used with Q203).
Composition: 2.7 ohms ±5%, 1/2 w.		19A134016P1	Insulated bushing. (Used with Q210).
Composition: 10 ohms ±5%, 1 w.		19All6023Pl	Insulated plate. (Used with Q210).
·		19A129361P1	Shield, (Located between L221-L222 and L222-L223).
Composition: 20 ohms ±5%, 1 w.		19A129361P2	Shield. (Located between L220-L221).
Composition 15 000 share 450 1/4 m			
Composition: 15,000 ohms ±5%, 1/4 w.			
Composition: 6800 ohms ±5%, 1/4 w.			
Composition: 100 ohms ±5%, 1/4 w.			
Metal film: 2150 ohms ±2%, 1/2 w.			
Metal film: 1470 ohms ±2%, 1/2 w. Metal film: 4220 ohms ±2%, 1/2 w.			
Metal film: 5110 ohms ±2%, 1/2 w.			
Metal film: 4220 ohms ±2%, 1/2 w.			
Variable, cermet: 5000 ohms ±20%, .5 w; sim to CTS Series 360.			
Composition: 680 ohms ±5%, 1/4 w.			
Composition: 560 ohms ±5%, 1/4 w.			
Composition: 1800 ohms ±5%, 1/4 w.			
Composition: 470 ohms ±5%, 1/2 w.			
Composition: 120 ohms ±5%, 1/2 w.			
Composition: 6800 ohms ±5%, 1/4 w.			
Composition: 3900 ohms ±5%, 1/4 w.			
Composition: 510 ohms ±5%, 1/4 w.			
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